- **Controlled Baseline**
  - **− One Assembly/Test Site, One Fabrication Site**
- **Extended Temperature Performance of −40°C to 125°C**
- **Enhanced Diminishing Manufacturing Sources (DMS) Support**
- **Enhanced Product-Change Notification**
- **Qualification Pedigree†**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 150 V (TLV2252/52A) and 100 V (TLV2254/54A) Using Machine Model (C = 200 pF, R = 0)**

† Component qualification in accordance with JEDEC and industry standards to ensure reliable operation over an extended temperature range. This includes, but is not limited to, Highly Accelerated Stress Test (HAST) or biased 85/85, temperature cycle, autoclave or unbiased HAST, electromigration, bond intermetallic life, and mold compound life. Such qualification testing should not be viewed as justifying use of this component beyond specified performance and environmental limits.

- **Output Swing Includes Both Supply Rails**
- **Low Noise . . . 19 nV/√Hz Typ at f = 1 kHz**
- **Low Input Bias Current . . . 1 pA Typ**
- **Fully Specified for Both Single-Supply and Split-Supply Operation**
- **Very Low Power . . . 34 µA Per Channel (Typ)**
- **Common-Mode Input Voltage Range Includes Negative Rail**
- **Low Input Offset Voltage: 850 µV Max at T_A = 25°C**
- **Wide Supply Voltage Range: 2.7 V to 16 V**
- **Macromodel Included**

description/ordering information

The TLV2252 and TLV2254 are dual and quadruple low-voltage operational amplifiers from Texas Instruments. Both devices exhibit rail-to-rail output performance for increased dynamic range in single- or split-supply applications. The TLV225x family consumes only 34 µA of supply current per channel. This micropower operation makes them good choices for battery-powered applications. This family is fully characterized at 3 V and 5 V and is optimized for low-voltage applications. The noise performance has been dramatically improved over previous generations of CMOS amplifiers. The TLV225x has a noise level of 19 nV/√Hz at 1kHz, four times lower than competitive micropower solutions.

The TLV225x, exhibiting high input impedance and low noise, are excellent for small-signal conditioning for high-impedance sources, such as piezoelectric transducers. Because of the micro-power dissipation levels combined with 3-V operation, these devices work well in hand-held monitoring and remote-sensing applications. In addition, the rail-to-rail output feature with single or split supplies makes this family a great choice when interfacing with analog-to-digital converters (ADCs). For precision applications, the TLV225xA family is available and has a maximum input offset voltage of 850 µV.

HIGH-LEVEL OUTPUT VOLTAGE vs HIGH-LEVEL OUTPUT CURRENT

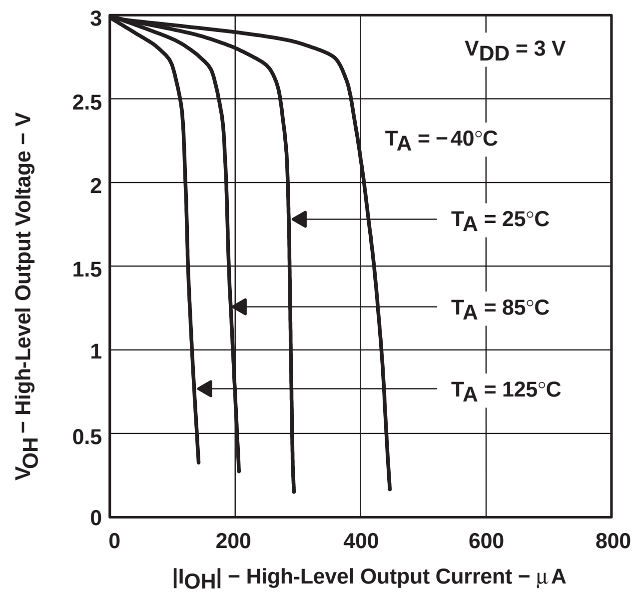


Figure 1

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

Advanced LinCMOS is a trademark of Texas Instruments.

description/ordering information (continued)

The TLV2252/2254 also make great upgrades to the TLV2322/2424 in standard designs. They offer increased output dynamic range, lower noise voltage, and lower input offset voltage. This enhanced feature set allows them to be used in a wider range of applications. For applications that require higher output drive and wider input voltage range, see the TLV2432 and TLV2442 devices. If your design requires single amplifiers, please see the TLV2211/21/31 family. These devices are single rail-to-rail operational amplifiers in the SOT-23 package. Small size and low power consumption make them ideal for high density, battery-powered equipment.

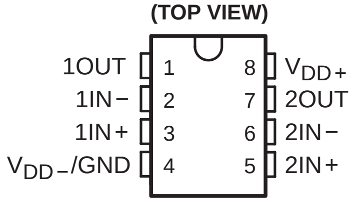
ORDERING INFORMATION

T_A	V_{IO}max AT 25°C	PACKAGE†		ORDERABLE PART NUMBER	TOP-SIDE MARKING
−40°C to 125°C	850 μV	SOIC (D)	Tape and reel	TLV2252AQDREP	2252AE
		TSSOP (PW)	Tape and reel	TLV2252AQPWREP‡	
	1500 μV	SOIC (D)	Tape and reel	TLV2252QDREP	2252EP
		TSSOP (PW)	Tape and reel	TLV2252QPWREP‡	
	850 μV	SOIC (D)	Tape and reel	TLV2254AQDREP	TLV2254AEP
		TSSOP (PW)	Tape and reel	TLV2254AQPWREP‡	
	1500 μV	SOIC (D)	Tape and reel	TLV2254QDREP	TLV2254EP
		TSSOP (PW)	Tape and reel	TLV2254QPWREP‡	

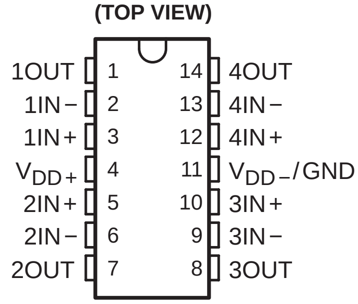
† Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

Product preview

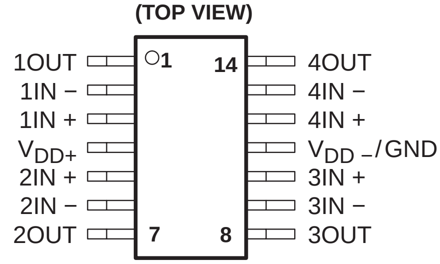
TLV2252, TLV2252A
D OR PW PACKAGE
(TOP VIEW)



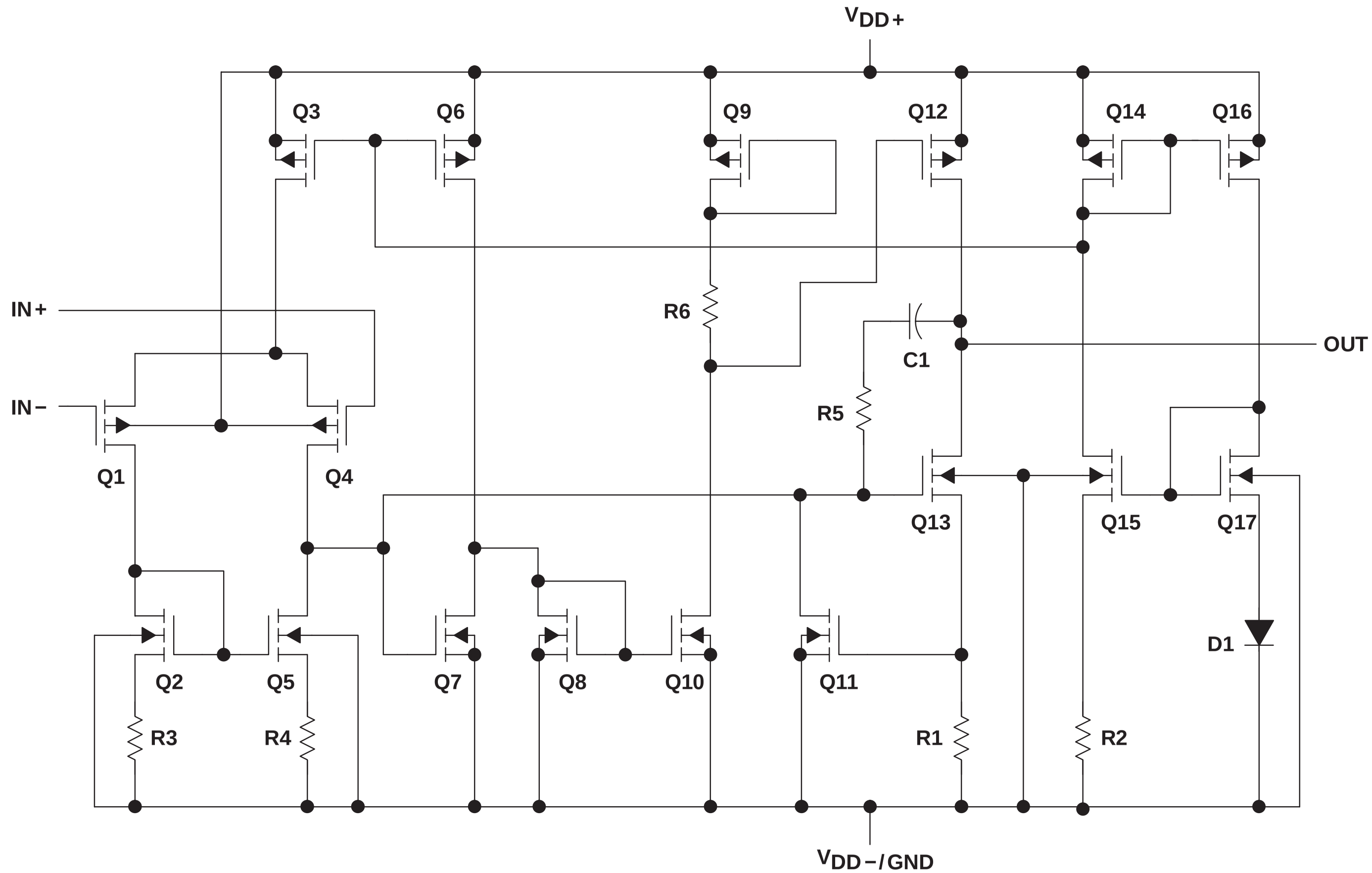
TLV2254, TLV2254A
D PACKAGE
(TOP VIEW)



TLV2254, TLV2254A
PW PACKAGE
(TOP VIEW)



equivalent schematic (each amplifier)



ACTUAL DEVICE COMPONENT COUNT†		
COMPONENT	TLV2252	TLV2254
Transistors	38	76
Resistors	30	56
Diodes	9	18
Capacitors	3	6

† Includes both amplifiers and all ESD, bias, and trim circuitry

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage, V_{DD} (see Note 1) . . . 16 V
Differential input voltage, V_{ID} (see Note 2) . . . $\pm V_{DD}$
Input voltage range, V_I (any input, see Note 1) . . . V_{DD-} − 0.3 V to V_{DD+}
Input current, I_I (each input) . . . ±5 mA
Output current, I_O . . . ±50 mA
Total current into V_{DD+} . . . ±50 mA
Total current out of V_{DD-} . . . ±50 mA
Duration of short-circuit current (at or below 25°C) (see Note 3) . . . Unlimited
Continuous total power dissipation . . . See Dissipation Rating Table
Operating free-air temperature range, T_A . . . −40°C to 125°C
Storage temperature range, T_{stg} . . . −65°C to 150°C
Lead temperature 1,6 mm (1/16 in) from case for 10 s . . . 260°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltage values, except differential voltages, are with respect to V_{DD-}.
2. Differential voltages are at the noninverting input with respect to the inverting input. Excessive current flows when input is brought below V_{DD-} − 0.3 V.
3. The output may be shorted to either supply. Temperature and/or supply voltages must be limited to ensure that the maximum dissipation rating is not exceeded.

DISSIPATION RATING TABLE

PACKAGE	$T_A \le 25°C$ POWER RATING	DERATING FACTOR ABOVE $T_A = 25°C$	$T_A = 85°C$ POWER RATING	$T_A = 125°C$ POWER RATING
D−8	725 mW	5.8 mW/°C	377 mW	145 mW
D−14	950 mW	7.6 mW/°C	494 mW	190 mW
PW−8	525 mW	4.2 mW/°C	273 mW	105 mW
PW−14	700 mW	5.6 mW/°C	364 mW	140 mW

recommended operating conditions

	MIN	MAX	UNIT
Supply voltage, V_{DD} (see Note 1)	2.7	8	V
Input voltage range, V_I	V_{DD-}	V_{DD+} −1.3	V
Common-mode input voltage, V_{IC}	V_{DD-}	V_{DD+} −1.3	V
Operating free-air temperature, T_A	−40	125	°C

NOTE 1: All voltage values, except differential voltages, are with respect to V_{DD-}.

TLV2252 electrical characteristics at specified free-air temperature, V_{DD} = 3 V (unless otherwise noted)

PARAMETER		TEST CONDITIONS	T_A†	TLV2252 MIN	TLV2252 TYP	TLV2252 MAX	TLV2252A MIN	TLV2252A TYP	TLV2252A MAX	UNIT
V_{IO}	Input offset voltage	$V_{DD\pm}$ = ±1.5 V, V_{IC} = 0, V_O = 0, R_S = 50 Ω	25°C		200	1500		200	850	µV
			Full range			1750			1000	
α_{VIO}	Temperature coefficient of input offset voltage	$V_{DD\pm}$ = ±1.5 V, V_{IC} = 0, V_O = 0, R_S = 50 Ω	25°C to 85°C		0.5			0.5		µV/°C
	Input offset voltage long-term drift (see Note 4)	$V_{DD\pm}$ = ±1.5 V, V_{IC} = 0, V_O = 0, R_S = 50 Ω	25°C		0.003			0.003		µV/mo
I_{IO}	Input offset current	$V_{DD\pm}$ = ±1.5 V, V_{IC} = 0, V_O = 0, R_S = 50 Ω	25°C		0.5	60		0.5	60	pA
			125°C			1000			1000	
I_{IB}	Input bias current	$V_{DD\pm}$ = ±1.5 V, V_{IC} = 0, V_O = 0, R_S = 50 Ω	25°C		1	60		1	60	pA
			125°C			1000			1000	
V_{ICR}	Common-mode input voltage range	R_S = 50 Ω, $\|V_{IO}\| \leq$ 5 mV	25°C	0 to 2	−0.3 to 2.2		0 to 2	−0.3 to 2.2		V
			Full range	0 to 1.7			0 to 1.7			
V_{OH}	High-level output voltage	I_{OH} = −20 µA	25°C		2.98			2.98		V
		I_{OH} = −75 µA	25°C	2.9			2.9			
			Full range	2.8			2.8			
		I_{OH} = −150 µA	25°C	2.8			2.8			
V_{OL}	Low-level output voltage	V_{IC} = 1.5 V, I_{OL} = 50 µA	25°C		10			10		mV
		V_{IC} = 1.5 V, I_{OL} = 500 µA	25°C		100	150		100	150	
			Full range			165			165	
		V_{IC} = 1.5 V, I_{OL} = 1 mA	25°C		200	300		200	300	
			Full range			300			300	
A_{VD}	Large-signal differential voltage amplification	V_{IC} = 1.5 V, V_O = 1 V to 2 V, R_L = 100 kΩ‡	25°C	100	250		100	250		V/mV
			Full range	10			10			
		V_{IC} = 1.5 V, V_O = 1 V to 2 V, R_L = 1 MΩ‡	25°C		800			800		
$r_{i(d)}$	Differential input resistance		25°C		10^{12}			10^{12}		Ω
$r_{i(c)}$	Common-mode input resistance		25°C		10^{12}			10^{12}		Ω
$c_{i(c)}$	Common-mode input capacitance	f = 10 kHz	25°C		8			8		pF
z_o	Closed-loop output impedance	f = 25 kHz, A_V = 10	25°C		220			220		Ω
CMRR	Common-mode rejection ratio	V_{IC} = 0 to 1.7 V, V_O = 1.5 V, R_S = 50 Ω	25°C	65	75		65	77		dB
			Full range	60			60			
k_{SVR}	Supply-voltage rejection ratio ($\Delta V_{DD} / \Delta V_{IO}$)	V_{DD} = 2.7 V to 8 V, $V_{IC} = V_{DD}/2$, No load	25°C	80	95		80	100		dB
			Full range	80			80			
I_{DD}	Supply current	V_O = 1.5 V, No load	25°C		68	125		68	125	µA
			Full range			150			150	

† Full range is −40°C to 125°C.
‡ Referenced to 1.5 V

NOTE 4: Typical values are based on the input offset voltage shift observed through 500 hours of operating life test at T_A = 150°C extrapolated to T_A = 25°C using the Arrhenius equation and assuming an activation energy of 0.96 eV.

TLV2252 operating characteristics at specified free-air temperature, V_{DD} = 3 V

PARAMETER		TEST CONDITIONS	T_A†	TLV2252			TLV2252A			UNIT
				MIN	TYP	MAX	MIN	TYP	MAX	
SR	Slew rate at unity gain	V_O = 0.8 V to 1.4 V, R_L = 100 kΩ‡, C_L = 100 pF‡	25°C	0.07	0.1		0.07	0.1		V/μs
			Full range	0.05			0.05			
V_n	Equivalent input noise voltage	f = 10 Hz	25°C		35			35		nV/√Hz
		f = 1 kHz			19			19		
$V_{N(PP)}$	Peak-to-peak equivalent input noise voltage	f = 0.1 Hz to 1 Hz	25°C		0.6			0.6		μV
		f = 0.1 Hz to 10 Hz			1.1			1.1		
I_n	Equivalent input noise current		25°C		0.6			0.6		fA /√Hz
	Gain-bandwidth product	f = 1 kHz, R_L = 50 kΩ‡, C_L = 100 pF‡	25°C		0.187			0.187		MHz
B_{OM}	Maximum output-swing bandwidth	$V_{O(PP)}$ = 1 V, A_V = 1, R_L = 50 kΩ‡, C_L = 100 pF‡	25°C		60			60		kHz
ϕ_m	Phase margin at unity gain	R_L = 50 kΩ‡, C_L = 100 pF‡	25°C		63°			63°		
	Gain margin	R_L = 50 kΩ‡, C_L = 100 pF‡	25°C		15			15		dB

† Full range is −40°C to 125°C.
‡ Referenced to 1.5 V

TLV2252 electrical characteristics at specified free-air temperature, V_{DD} = 5 V (unless otherwise noted)

PARAMETER		TEST CONDITIONS	T_A†	TLV2252			TLV2252A			UNIT
				MIN	TYP	MAX	MIN	TYP	MAX	
V_{IO}	Input offset voltage	$V_{DD\pm}$ = ±2.5 V, V_{IC} = 0, V_O = 0, R_S = 50 Ω	25°C		200	1500		200	850	µV
			Full range			1750			1000	
α_{VIO}	Temperature coefficient of input offset voltage	$V_{DD\pm}$ = ±2.5 V, V_{IC} = 0, V_O = 0, R_S = 50 Ω	25°C to 85°C		0.5			0.5		µV/°C
	Input offset voltage long-term drift (see Note 4)	$V_{DD\pm}$ = ±2.5 V, V_{IC} = 0, V_O = 0, R_S = 50 Ω	25°C		0.003			0.003		µV/mo
I_{IO}	Input offset current	$V_{DD\pm}$ = ±2.5 V, V_{IC} = 0, V_O = 0, R_S = 50 Ω	25°C		0.5	60		0.5	60	pA
			125°C			1000			1000	
I_{IB}	Input bias current	$V_{DD\pm}$ = ±2.5 V, V_{IC} = 0, V_O = 0, R_S = 50 Ω	25°C		1	60		1	60	pA
			125°C			1000			1000	
V_{ICR}	Common-mode input voltage range	$\lvert V_{IO}\rvert$ ≤ 5 mV, R_S = 50 Ω	25°C	0 to 4	−0.3 to 4.2		0 to 4	−0.3 to 4.2		V
			Full range	0 to 3.5			0 to 3.5			
V_{OH}	High-level output voltage	I_{OH} = −20 µA	25°C		4.98			4.98		V
		I_{OH} = −75 µA	25°C	4.9	4.94		4.9	4.94		
			Full range	4.8			4.8			
		I_{OH} = −150 µA	25°C	4.8	4.88		4.8	4.88		
V_{OL}	Low-level output voltage	V_{IC} = 2.5 V, I_{OL} = 50 µA	25°C		0.01			0.01		V
		V_{IC} = 2.5 V, I_{OL} = 500 µA	25°C		0.09	0.15		0.09	0.15	
			Full range			0.15			0.15	
		V_{IC} = 2.5 V, I_{OL} = 1 mA	25°C		0.2	0.3		0.2	0.3	
			Full range			0.3			0.3	
A_{VD}	Large-signal differential voltage amplification	V_{IC} = 2.5 V, V_O = 1 V to 4 V, R_L = 100 kΩ‡	25°C	100	350		100	350		V/mV
			Full range	10			10			
		V_{IC} = 2.5 V, V_O = 1 V to 4 V, R_L = 1 MΩ‡	25°C		1700			1700		
$r_{i(d)}$	Differential input resistance		25°C		10^{12}			10^{12}		Ω
$r_{i(c)}$	Common-mode input resistance		25°C		10^{12}			10^{12}		Ω
$c_{i(c)}$	Common-mode input capacitance	f = 10 kHz	25°C		8			8		pF
z_o	Closed-loop output impedance	f = 25 kHz, A_V = 10	25°C		200			200		Ω
CMRR	Common-mode rejection ratio	V_{IC} = 0 to 2.7 V, V_O = 2.5 V, R_S = 50 Ω	25°C	70	83		70	83		dB
			Full range	70			70			
k_{SVR}	Supply-voltage rejection ratio ($\Delta V_{DD}/\Delta V_{IO}$)	V_{DD} = 4.4 V to 8 V, V_{IC} = V_{DD}/2, No load	25°C	80	95		80	95		dB
			Full range	80			80			

† Full range is −40°C to 125°C.
‡ Referenced to 2.5 V

NOTE 4: Typical values are based on the input offset voltage shift observed through 500 hours of operating life test at T_A = 150°C extrapolated to T_A = 25°C using the Arrhenius equation and assuming an activation energy of 0.96 eV.

TLV2252 electrical characteristics at specified free-air temperature, V_{DD} = 5 V (unless otherwise noted) (continued)

PARAMETER		TEST CONDITIONS		T_A†	TLV2252			TLV2252A			UNIT
					MIN	TYP	MAX	MIN	TYP	MAX	
I_{DD}	Supply current	V_O = 2.5 V,	No load	25°C		70	125		70	125	µA
				Full range			150			150	

† Full range is −40°C to 125°C for Q level part.

TLV2252 operating characteristics at specified free-air temperature, V_{DD} = 5 V

PARAMETER		TEST CONDITIONS		T_A†	TLV2252			TLV2252A			UNIT
					MIN	TYP	MAX	MIN	TYP	MAX	
SR	Slew rate at unity gain	V_O = 1.25 V to 2.75 V, R_L = 100 kΩ‡, C_L = 100 pF‡		25°C	0.07	0.12		0.07	0.12		V/µs
				Full range	0.05			0.05			
V_n	Equivalent input noise voltage	f = 10 Hz		25°C		36			36		nV/√Hz
		f = 1 kHz		25°C		19			19		
$V_{N(PP)}$	Peak-to-peak equivalent input noise voltage	f = 0.1 Hz to 1 Hz		25°C		0.7			0.7		µV
		f = 0.1 Hz to 10 Hz		25°C		1.1			1.1		
I_n	Equivalent input noise current			25°C		0.6			0.6		fA/√Hz
THD+N	Total harmonic distortion plus noise	V_O = 0.5 V to 2.5 V, f = 20 kHz, R_L = 50 kΩ‡	A_V = 1	25°C		0.2%			0.2%		
			A_V = 10			1%			1%		
	Gain-bandwidth product	f = 50 kHz, C_L = 100 pF‡	R_L = 50 kΩ‡,	25°C		0.2			0.2		MHz
B_{OM}	Maximum output-swing bandwidth	$V_{O(PP)}$ = 2 V, R_L = 50 kΩ‡,	A_V = 1, C_L = 100 pF‡	25°C		30			30		kHz
ϕ_m	Phase margin at unity gain	R_L = 50 kΩ‡,	C_L = 100 pF‡	25°C		63°			63°		
	Gain margin	R_L = 50 kΩ‡,	C_L = 100 pF‡	25°C		15			15		dB

† Full range is −40°C to 125°C.
‡ Referenced to 2.5 V

TLV2254 electrical characteristics at specified free-air temperature, V_{DD} = 3 V (unless otherwise noted)

PARAMETER		TEST CONDITIONS		T_A†	TLV2254 MIN	TLV2254 TYP	TLV2254 MAX	TLV2254A MIN	TLV2254A TYP	TLV2254A MAX	UNIT
V_{IO}	Input offset voltage	$V_{DD\pm}$ = ±1.5 V, V_O = 0,	V_{IC} = 0, R_S = 50 Ω	25°C		200	1500		200	850	μV
				Full range			1750			1000	
α_{VIO}	Temperature coefficient of input offset voltage	$V_{DD\pm}$ = ±1.5 V, V_O = 0,	V_{IC} = 0, R_S = 50 Ω	25°C to 125°C		0.5			0.5		μV/°C
	Input offset voltage long-term drift (see Note 4)	$V_{DD\pm}$ = ±1.5 V, V_O = 0,	V_{IC} = 0, R_S = 50 Ω	25°C		0.003			0.003		μV/mo
I_{IO}	Input offset current	$V_{DD\pm}$ = ±1.5 V, V_O = 0,	V_{IC} = 0, R_S = 50 Ω	25°C		0.5	60		0.5	60	pA
				125°C			1000			1000	
I_{IB}	Input bias current	$V_{DD\pm}$ = ±1.5 V, V_O = 0,	V_{IC} = 0, R_S = 50 Ω	25°C		1	60		1	60	pA
				125°C			1000			1000	
V_{ICR}	Common-mode input voltage range	R_S = 50 Ω,	$\|V_{IO}\| \le$ 5 mV	25°C	0 to 2	−0.3 to 2.2		0 to 2	−0.3 to 2.2		V
				Full range	0 to 1.7			0 to 1.7			
V_{OH}	High-level output voltage	I_{OH} = −20 μA		25°C		2.98			2.98		V
		I_{OH} = −75 μA		25°C	2.9			2.9			
				Full range	2.8			2.8			
		I_{OH} = −150 μA		25°C	2.8			2.8			
V_{OL}	Low-level output voltage	V_{IC} = 1.5 V,	I_{OL} = 50 μA	25°C		10			10		mV
		V_{IC} = 1.5 V,	I_{OL} = 500 μA	25°C		100	150		100	150	
				Full range			165			165	
		V_{IC} = 1.5 V,	I_{OL} = 1 mA	25°C		200	300		200	300	
				Full range			300			300	
A_{VD}	Large-signal differential voltage amplification	V_{IC} = 1.5 V, V_O = 1 V to 2 V	R_L = 100 kΩ‡	25°C	100	225		100	225		V/mV
				Full range	10			10			
			R_L = 1 MΩ‡	25°C		800			800		
$r_{i(d)}$	Differential input resistance			25°C		10^{12}			10^{12}		Ω
$r_{i(c)}$	Common-mode input resistance			25°C		10^{12}			10^{12}		Ω
$c_{i(c)}$	Common-mode input capacitance	f = 10 kHz		25°C		8			8		pF
z_o	Closed-loop output impedance	f = 25 kHz,	A_V = 10	25°C		220			220		Ω
CMRR	Common-mode rejection ratio	V_{IC} = 0 to 1.7 V, R_S = 50 Ω	V_O = 1.5 V,	25°C	65	75		65	77		dB
				Full range	60			60			
k_{SVR}	Supply-voltage rejection ratio ($\Delta V_{DD}/\Delta V_{IO}$)	V_{DD} = 2.7 V to 8 V, V_{IC} = V_{DD}/2,	No load	25°C	80	95		80	100		dB
				Full range	80			80			

† Full range is −40°C to 125°C.
‡ Referenced to 1.5 V
NOTE 4: Typical values are based on the input offset voltage shift observed through 500 hours of operating life test at T_A = 150°C extrapolated to T_A = 25°C using the Arrhenius equation and assuming an activation energy of 0.96 eV.

TLV2254 electrical characteristics at specified free-air temperature, V_{DD} = 3 V (unless otherwise noted) (continued)

PARAMETER		TEST CONDITIONS		T_A†	TLV2254			TLV2254A			UNIT
					MIN	TYP	MAX	MIN	TYP	MAX	
I_{DD}	Supply current (four amplifiers)	V_O = 1.5 V,	No load	25°C		135	250		135	250	µA
				Full range			300			300	

† Full range is −40°C to 125°C for Q level part.

TLV2254 operating characteristics at specified free-air temperature, V_{DD} = 3 V

PARAMETER		TEST CONDITIONS	T_A†	TLV2254			TLV2254A			UNIT
				MIN	TYP	MAX	MIN	TYP	MAX	
SR	Slew rate at unity gain	V_O = 0.5 V to 1.7 V, R_L = 100 kΩ‡, C_L = 100 pF‡	25°C	0.07	0.1		0.07	0.1		V/µs
			Full range	0.05			0.05			
V_n	Equivalent input noise voltage	f = 10 Hz	25°C		35			35		nV/√Hz
		f = 1 kHz			19			19		
$V_{N(PP)}$	Peak-to-peak equivalent input noise voltage	f = 0.1 Hz to 1 Hz	25°C		0.6			0.6		µV
		f = 0.1 Hz to 10 Hz			1.1			1.1		
I_n	Equivalent input noise current		25°C		0.6			0.6		fA/√Hz
	Gain-bandwidth product	f = 1 kHz, R_L = 50 kΩ‡, C_L = 100 pF‡	25°C		0.187			0.187		MHz
B_{OM}	Maximum output-swing bandwidth	$V_{O(PP)}$ = 1 V, A_V = 1, R_L = 50 kΩ‡, C_L = 100 pF‡	25°C		60			60		kHz
ϕ_m	Phase margin at unity gain	R_L = 50 kΩ‡, C_L = 100 pF‡	25°C		63°			63°		
	Gain margin	R_L = 50 kΩ‡, C_L = 100 pF‡	25°C		15			15		dB

† Full range is −40°C to 125°C for Q level part.
‡ Referenced to 1.5 V

TLV2254 electrical characteristics at specified free-air temperature, V_{DD} = 5 V (unless otherwise noted)

PARAMETER		TEST CONDITIONS	T_A†	TLV2254 MIN	TLV2254 TYP	TLV2254 MAX	TLV2254A MIN	TLV2254A TYP	TLV2254A MAX	UNIT
V_{IO}	Input offset voltage	$V_{DD\pm}$ = ±2.5 V, V_{IC} = 0, V_O = 0, R_S = 50 Ω	25°C		200	1500		200	850	μV
			Full range			1750			1000	
α_{VIO}	Temperature coefficient of input offset voltage	$V_{DD\pm}$ = ±2.5 V, V_{IC} = 0, V_O = 0, R_S = 50 Ω	25°C to 125°C		0.5			0.5		μV/°C
	Input offset voltage long-term drift (see Note 4)	$V_{DD\pm}$ = ±2.5 V, V_{IC} = 0, V_O = 0, R_S = 50 Ω	25°C		0.003			0.003		μV/mo
I_{IO}	Input offset current	$V_{DD\pm}$ = ±2.5 V, V_{IC} = 0, V_O = 0, R_S = 50 Ω	25°C		0.5	60		0.5	60	pA
			125°C			1000			1000	
I_{IB}	Input bias current	$V_{DD\pm}$ = ±2.5 V, V_{IC} = 0, V_O = 0, R_S = 50 Ω	25°C		1	60		1	60	pA
			125°C			1000			1000	
V_{ICR}	Common-mode input voltage range	$\|V_{IO}\| \le$ 5 mV, R_S = 50 Ω	25°C	0 to 4	−0.3 to 4.2		0 to 4	−0.3 to 4.2		V
			Full range	0 to 3.5			0 to 3.5			
V_{OH}	High-level output voltage	I_{OH} = −20 μA	25°C		4.98			4.98		V
		I_{OH} = −75 μA	25°C	4.9	4.94		4.9	4.94		
			Full range	4.8			4.8			
		I_{OH} = −150 μA	25°C	4.8	4.88		4.8	4.88		
V_{OL}	Low-level output voltage	V_{IC} = 2.5 V, I_{OL} = 50 μA	25°C		0.01			0.01		V
		V_{IC} = 2.5 V, I_{OL} = 500 μA	25°C		0.09	0.15		0.09	0.15	
			Full range			0.15			0.15	
		V_{IC} = 2.5 V, I_{OL} = 1 mA	25°C		0.2	0.3		0.2	0.3	
			Full range			0.3			0.3	
A_{VD}	Large-signal differential voltage amplification	V_{IC} = 2.5 V, V_O = 1 V to 4 V, R_L = 100 kΩ‡	25°C	100	350		100	350		V/mV
			Full range	10			10			
		V_{IC} = 2.5 V, V_O = 1 V to 4 V, R_L = 1 MΩ‡	25°C		1700			1700		
$r_{i(d)}$	Differential input resistance		25°C		10^{12}			10^{12}		Ω
$r_{i(c)}$	Common-mode input resistance		25°C		10^{12}			10^{12}		Ω
$c_{i(c)}$	Common-mode input capacitance	f = 10 kHz	25°C		8			8		pF
z_o	Closed-loop output impedance	f = 25 kHz, A_V = 10	25°C		200			200		Ω
CMRR	Common-mode rejection ratio	V_{IC} = 0 to 2.7 V, V_O = 2.5 V, R_S = 50 Ω	25°C	70	83		70	83		dB
			Full range	70			70			
k_{SVR}	Supply-voltage rejection ratio ($\Delta V_{DD}/\Delta V_{IO}$)	V_{DD} = 4.4 V to 8 V, V_{IC} = V_{DD}/2, No load	25°C	80	95		80	95		dB
			Full range	80			80			

† Full range is −40°C to 125°C.
‡ Referenced to 2.5 V

NOTE 4: Typical values are based on the input offset voltage shift observed through 500 hours of operating life test at T_A = 150°C extrapolated to T_A = 25°C using the Arrhenius equation and assuming an activation energy of 0.96 eV.

TLV2254 electrical characteristics at specified free-air temperature, V_{DD} = 5 V (unless otherwise noted) (continued)

PARAMETER		TEST CONDITIONS		T_A†	TLV2254			TLV2254A			UNIT
					MIN	TYP	MAX	MIN	TYP	MAX	
I_{DD}	Supply current (four amplifiers)	V_O = 2.5 V,	No load	25°C		140	250		140	250	µA
				Full range			300			300	

† Full range is −40°C to 125°C.

TLV2254 operating characteristics at specified free-air temperature, V_{DD} = 5 V

PARAMETER		TEST CONDITIONS		T_A†	TLV2254			TLV2254A			UNIT
					MIN	TYP	MAX	MIN	TYP	MAX	
SR	Slew rate at unity gain	V_O = 0.5 V to 3.5 V, C_L = 100 pF‡	R_L = 100 kΩ‡,	25°C	0.07	0.12		0.07	0.12		V/µs
				Full range	0.05			0.05			
V_n	Equivalent input noise voltage	f = 10 Hz		25°C		36			36		nV/√Hz
		f = 1 kHz				19			19		
$V_{N(PP)}$	Peak-to-peak equivalent input noise voltage	f = 0.1 Hz to 1 Hz		25°C		0.7			0.7		µV
		f = 0.1 Hz to 10 Hz				1.1			1.1		
I_n	Equivalent input noise current			25°C		0.6			0.6		fA/√Hz
THD+N	Total harmonic distortion plus noise	V_O = 0.5 V to 2.5 V, f = 20 kHz, R_L = 50 kΩ‡	A_V = 1	25°C		0.2%			0.2%		
			A_V = 10			1%			1%		
	Gain-bandwidth product	f = 50 kHz, C_L = 100 pF‡	R_L = 50 kΩ‡,	25°C		0.2			0.2		MHz
B_{OM}	Maximum output-swing bandwidth	$V_{O(PP)}$ = 2 V, R_L = 50 kΩ‡,	A_V = 1, C_L = 100 pF‡	25°C		30			30		kHz
ϕ_m	Phase margin at unity gain	R_L = 50 kΩ‡,	C_L = 100 pF‡	25°C		63°			63°		
	Gain margin	R_L = 50 kΩ‡,	C_L = 100 pF‡	25°C		15			15		dB

† Full range is −40°C to 125°C for Q level part.
‡ Referenced to 2.5 V

TYPICAL CHARACTERISTICS

Table of Graphs

			FIGURE
V_{IO}	Input offset voltage	Distribution vs Common-mode voltage	2−5 6, 7
α_{VIO}	Input offset voltage temperature coefficient	Distribution	8−11
I_{IB}/I_{IO}	Input bias and input offset currents	vs Free-air temperature	12
V_I	Input voltage	vs Supply voltage vs Free-air temperature	13 14
V_{OH}	High-level output voltage	vs High-level output current	15, 18
V_{OL}	Low-level output voltage	vs Low-level output current	16, 17, 19
$V_{O(PP)}$	Maximum peak-to-peak output voltage	vs Frequency	20
I_{OS}	Short-circuit output current	vs Supply voltage vs Free-air temperature	21 22
V_{ID}	Differential input voltage	vs Output voltage	23, 24
A_{VD}	Differential voltage amplification	vs Load resistance	25
A_{VD}	Large-signal differential voltage amplification	vs Frequency vs Free-air temperature	26, 27 28, 29
z_o	Output impedance	vs Frequency	30, 31
CMRR	Common-mode rejection ratio	vs Frequency vs Free-air temperature	32 33
k_{SVR}	Supply-voltage rejection ratio	vs Frequency vs Free-air temperature	34, 35 36
I_{DD}	Supply current	vs Supply voltage	37, 38
SR	Slew rate	vs Load capacitance vs Free-air temperature	39 40
V_O	Inverting large-signal pulse response		41, 42
V_O	Voltage-follower large-signal pulse response		43, 44
V_O	Inverting small-signal pulse response		45, 46
V_O	Voltage-follower small-signal pulse response		47, 48
V_n	Equivalent input noise voltage	vs Frequency	49, 50
	Input noise voltage	Over a 10-s period	51
	Integrated noise voltage	vs Frequency	52
THD+N	Total harmonic distortion plus noise	vs Frequency	53
	Gain-bandwidth product	vs Supply voltage vs Free-air temperature	54 55
ϕ_m	Phase margin	vs Frequency vs Load capacitance	26, 27 56
	Gain margin	vs Load capacitance	57
B_1	Unity-gain bandwidth	vs Load capacitance	58
	Overestimation of phase margin	vs Load capacitance	59

TYPICAL CHARACTERISTICS

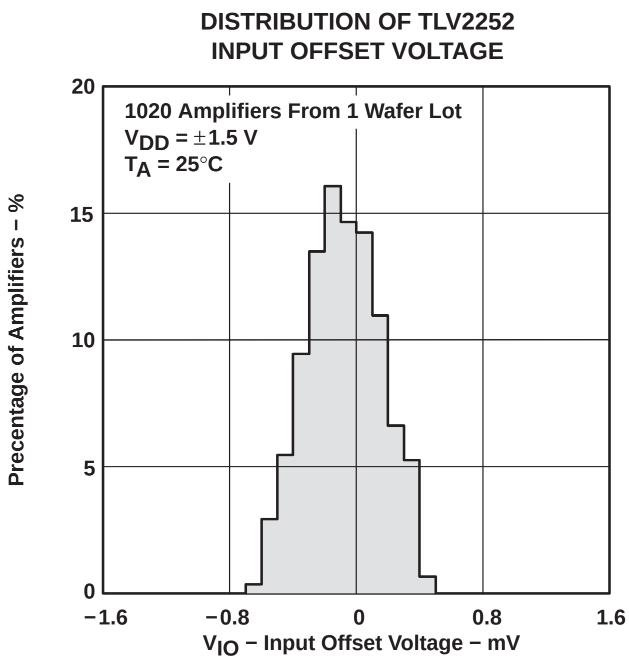


Figure 2

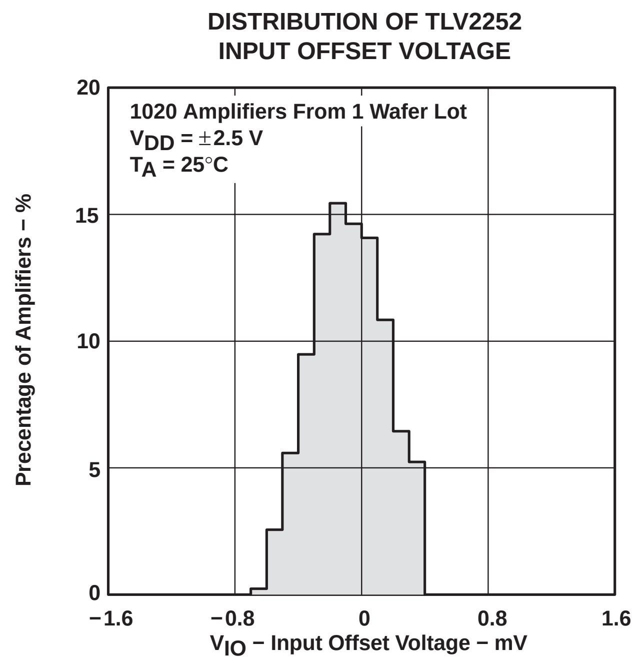


Figure 3

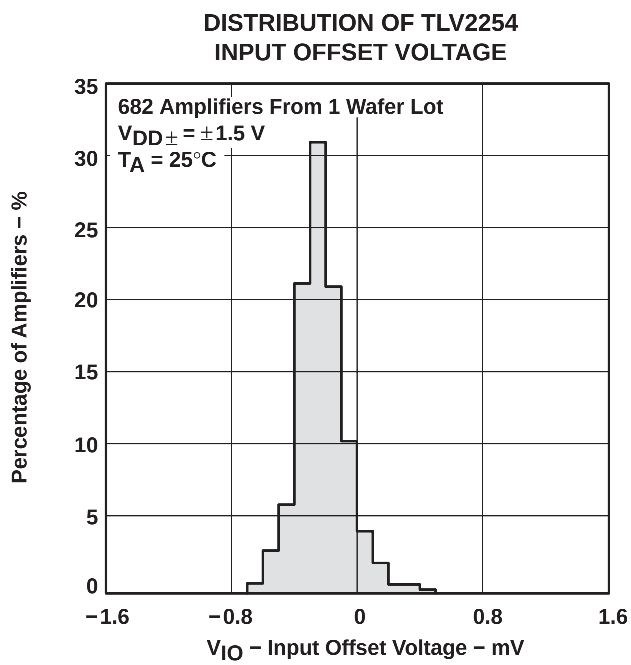


Figure 4

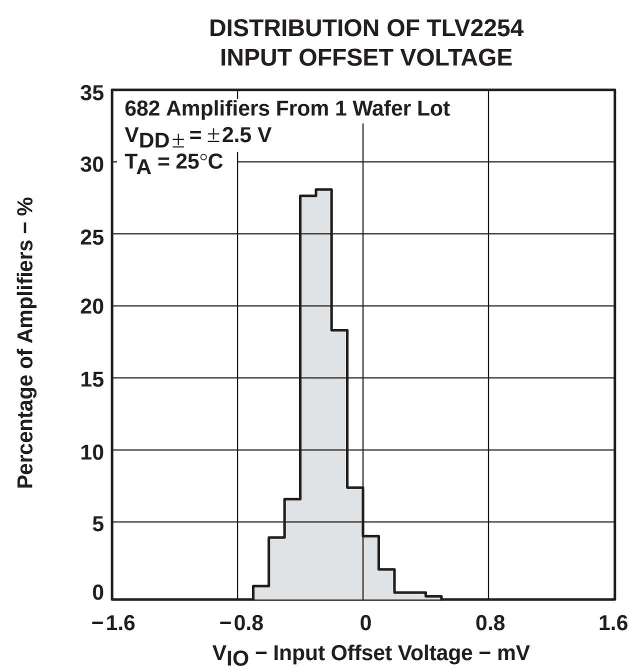


Figure 5

TYPICAL CHARACTERISTICS

INPUT OFFSET VOLTAGE†
vs
COMMON-MODE INPUT VOLTAGE

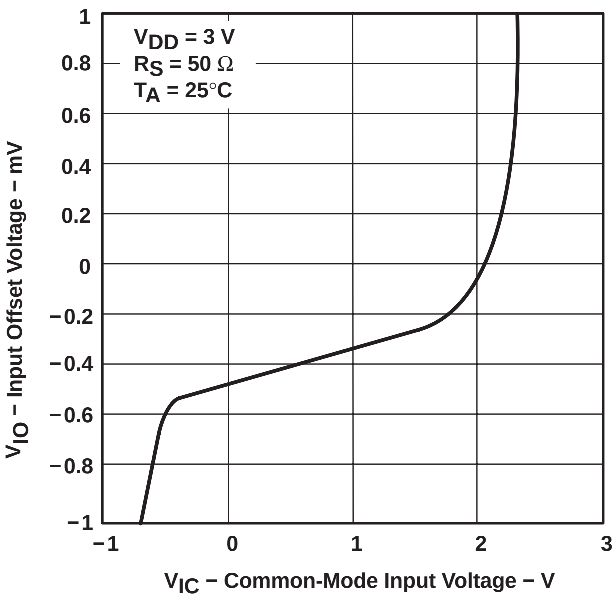


Figure 6

INPUT OFFSET VOLTAGE†
vs
COMMON-MODE INPUT VOLTAGE

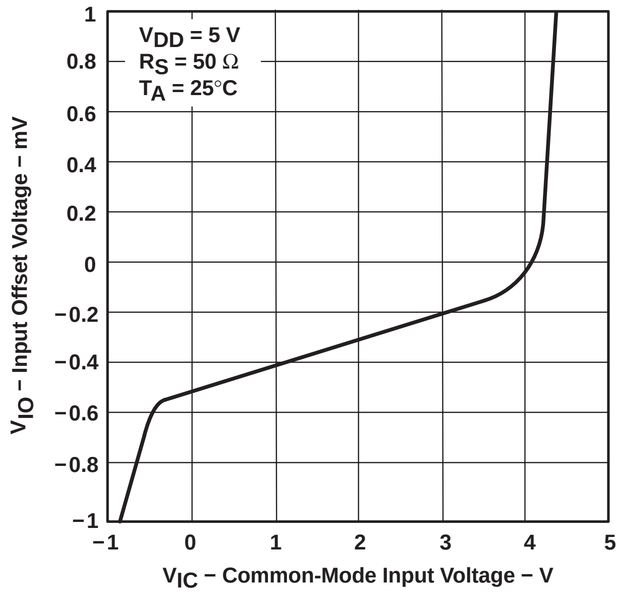


Figure 7

DISTRIBUTION OF TLV2252 INPUT OFFSET
VOLTAGE TEMPERATURE COEFFICIENT†

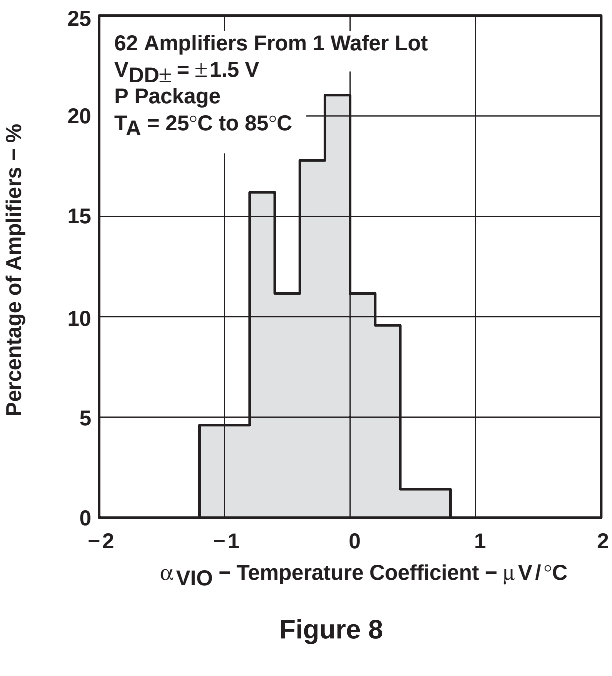


Figure 8

DISTRIBUTION OF TLV2252 INPUT OFFSET
VOLTAGE TEMPERATURE COEFFICIENT†

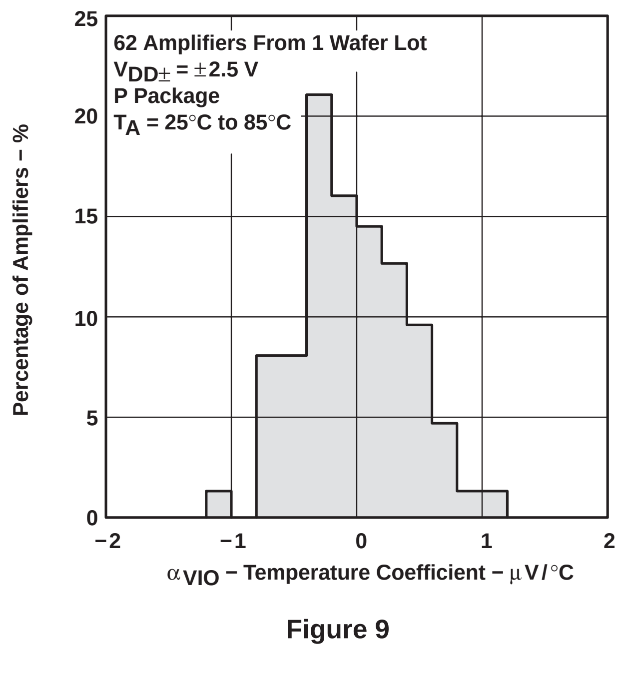


Figure 9

† For all curves where V_{DD} = 5 V, all loads are referenced to 2.5 V. For all curves where V_{DD} = 3 V, all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

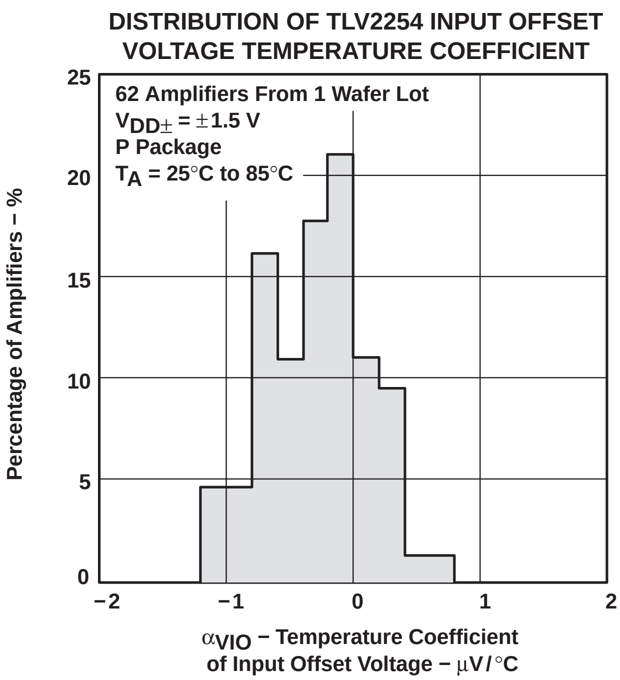


Figure 10

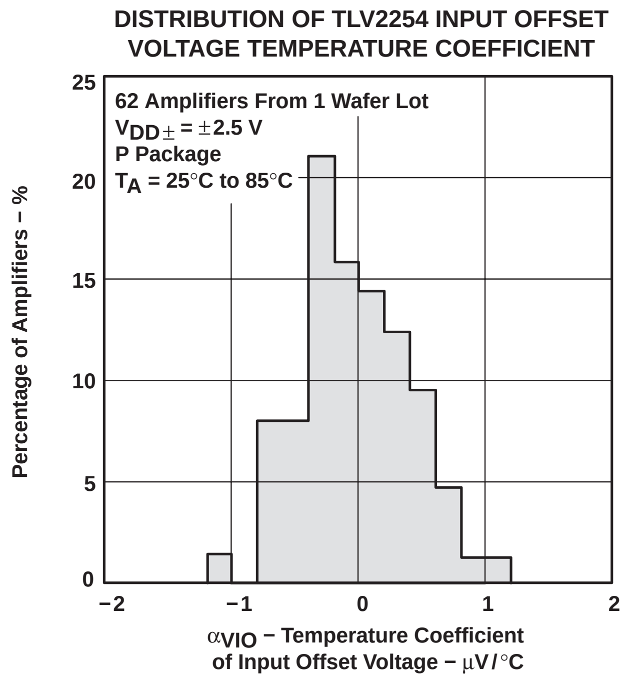


Figure 11

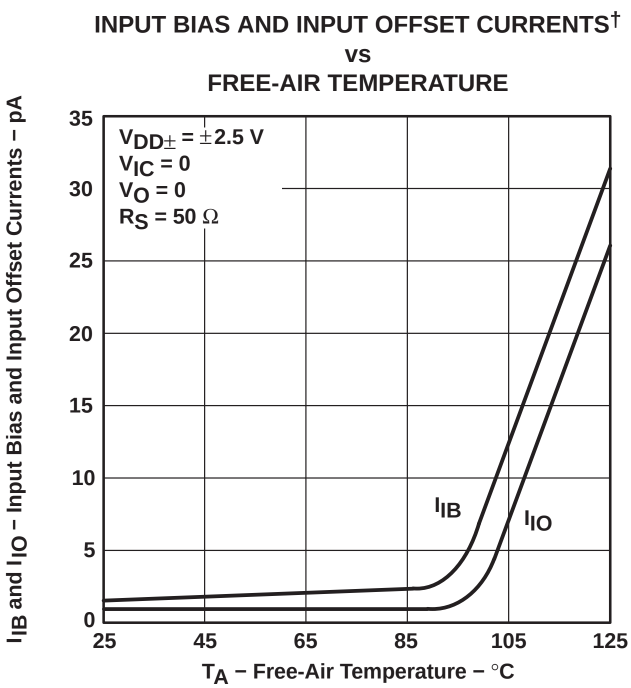


Figure 12

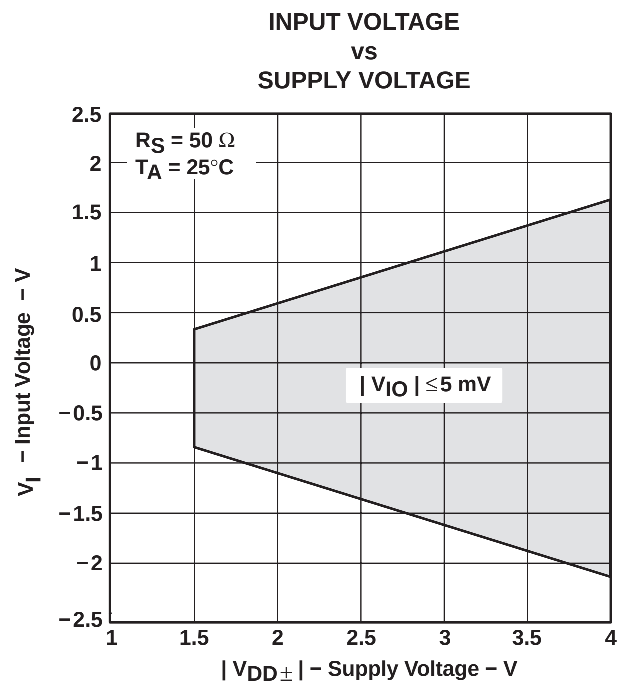


Figure 13

† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

TYPICAL CHARACTERISTICS

INPUT VOLTAGE†‡ vs FREE-AIR TEMPERATURE

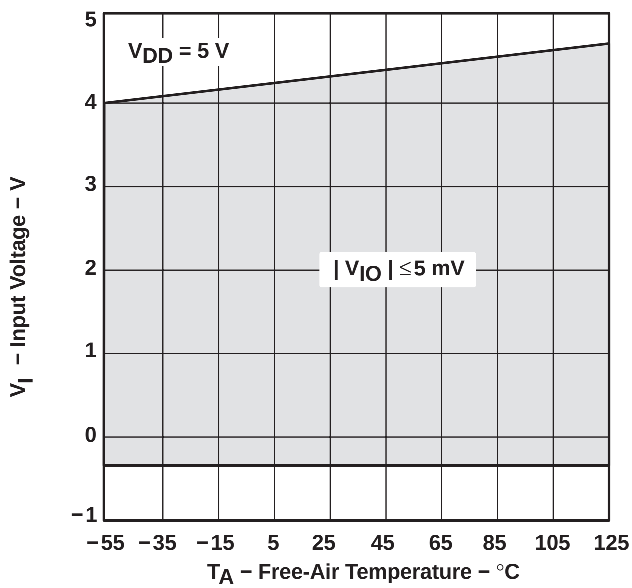


Figure 14

HIGH-LEVEL OUTPUT VOLTAGE†‡ vs HIGH-LEVEL OUTPUT CURRENT

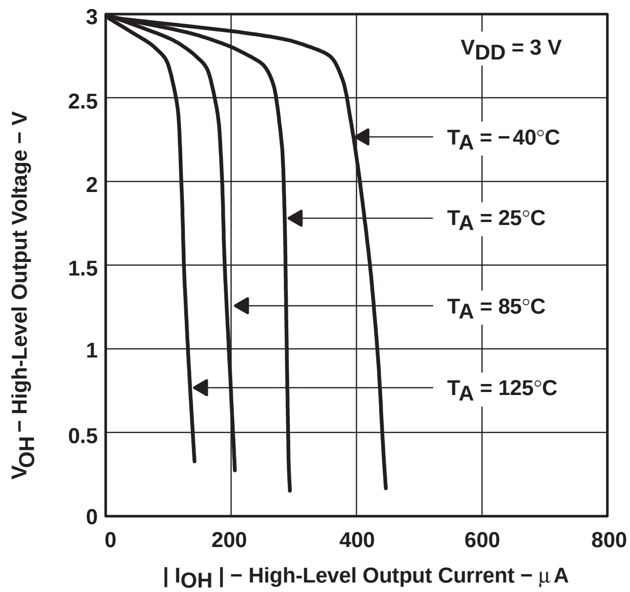


Figure 15

LOW-LEVEL OUTPUT VOLTAGE‡ vs LOW-LEVEL OUTPUT CURRENT

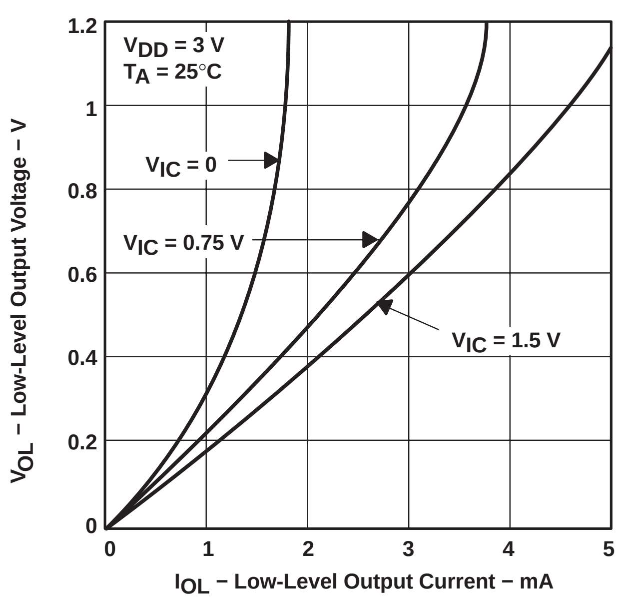


Figure 16

LOW-LEVEL OUTPUT VOLTAGE†‡ vs LOW-LEVEL OUTPUT CURRENT

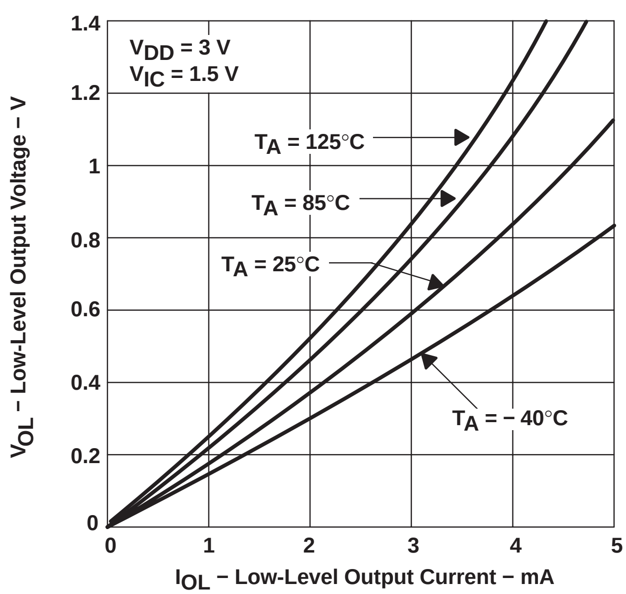


Figure 17

† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.
‡ For all curves where V_{DD} = 5 V, all loads are referenced to 2.5 V. For all curves where V_{DD} = 3 V, all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

HIGH-LEVEL OUTPUT VOLTAGE†‡ vs HIGH-LEVEL OUTPUT CURRENT

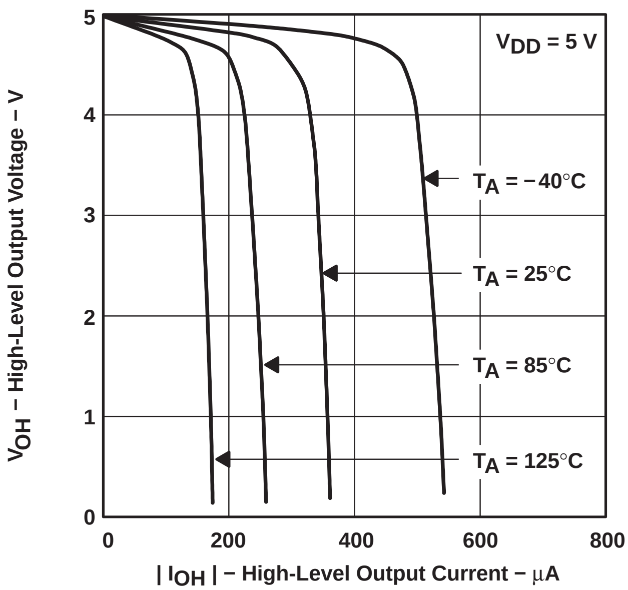


Figure 18

LOW-LEVEL OUTPUT VOLTAGE†‡ vs LOW-LEVEL OUTPUT CURRENT

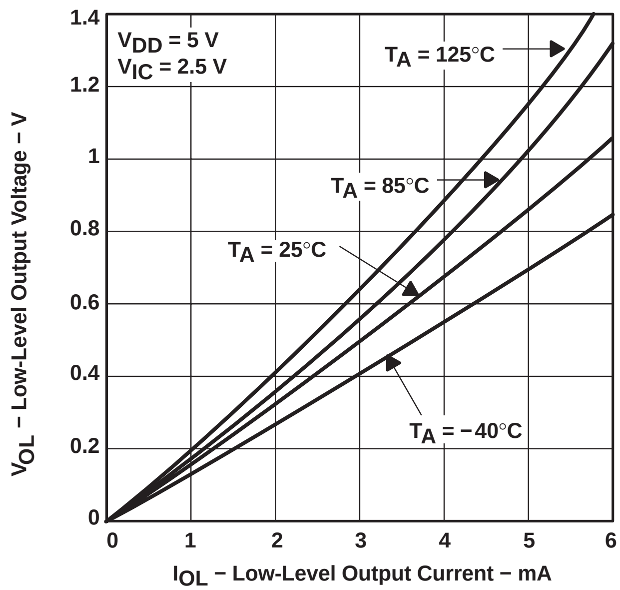


Figure 19

MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE‡ vs FREQUENCY

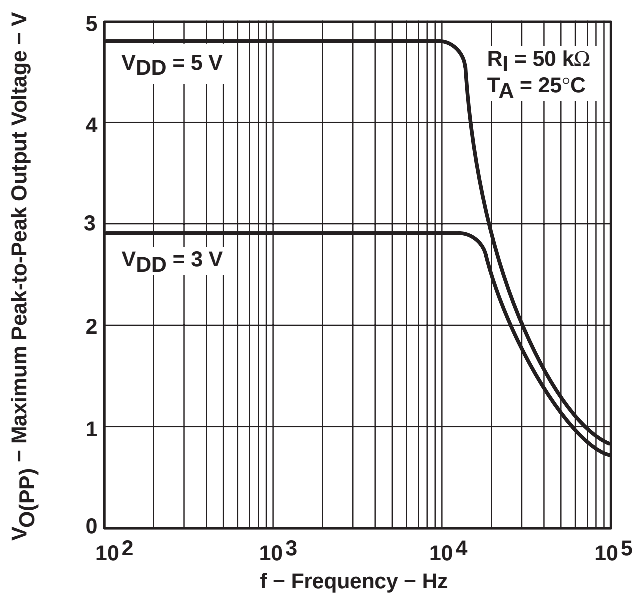


Figure 20

SHORT-CIRCUIT OUTPUT CURRENT vs SUPPLY VOLTAGE

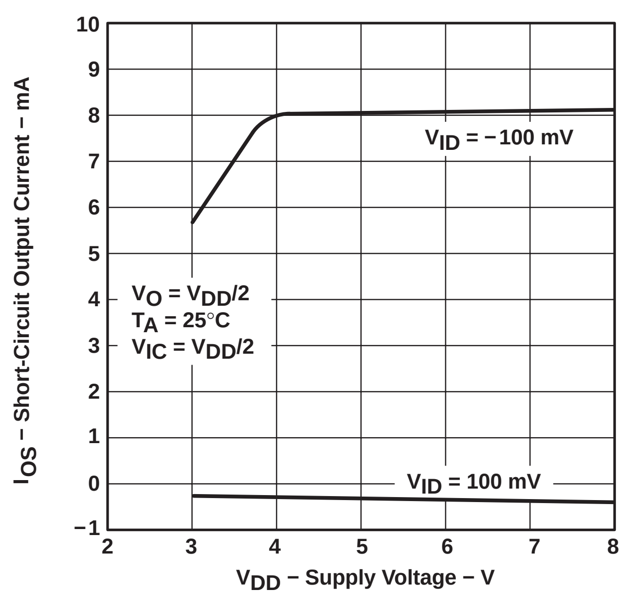


Figure 21

† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.
‡ For all curves where V_{DD} = 5 V, all loads are referenced to 2.5 V. For all curves where V_{DD} = 3 V, all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

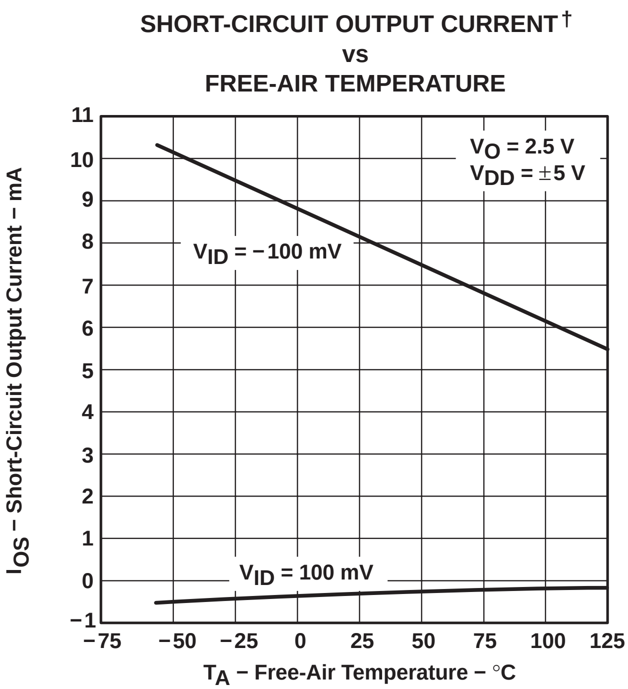


Figure 22

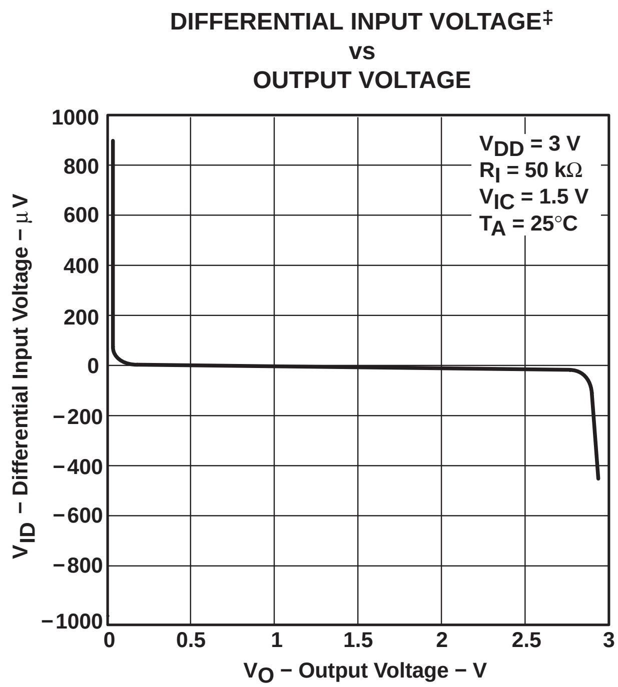


Figure 23

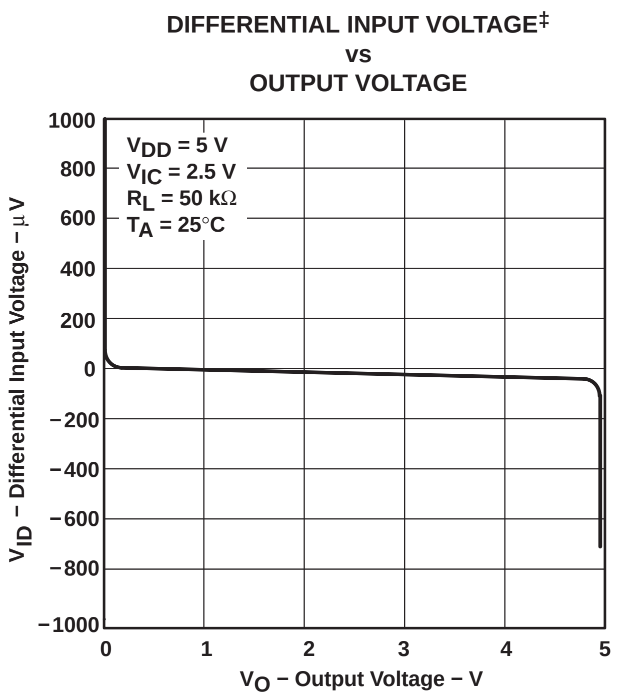


Figure 24

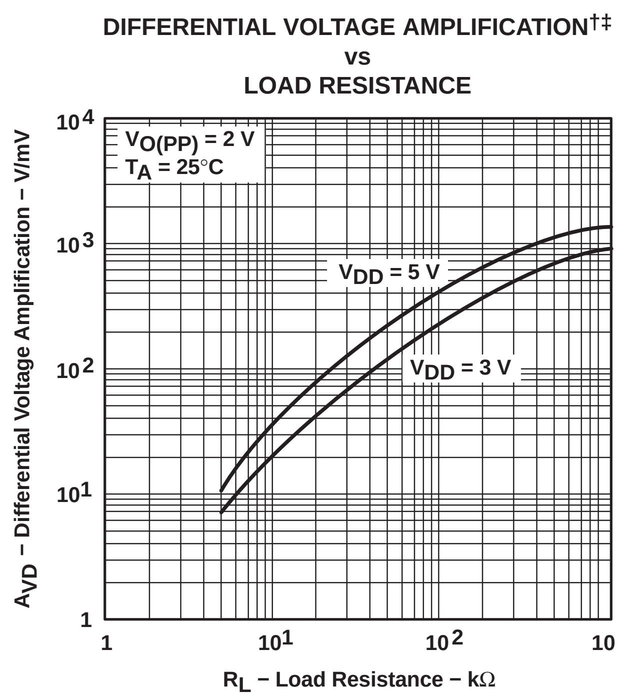


Figure 25

† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.
‡ For all curves where V_{DD} = 5 V, all loads are referenced to 2.5 V. For all curves where V_{DD} = 3 V, all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

LARGE-SIGNAL DIFFERENTIAL VOLTAGE† AMPLIFICATION AND PHASE MARGIN vs FREQUENCY

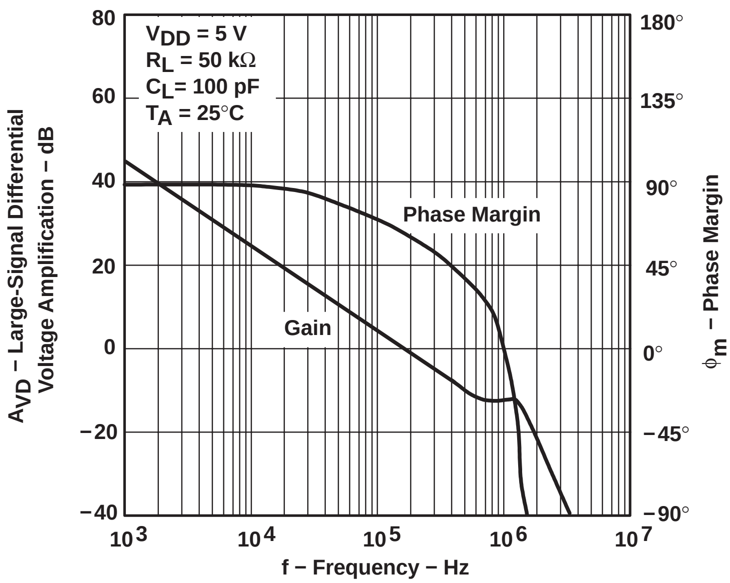


Figure 26

LARGE-SIGNAL DIFFERENTIAL VOLTAGE† AMPLIFICATION AND PHASE MARGIN vs FREQUENCY

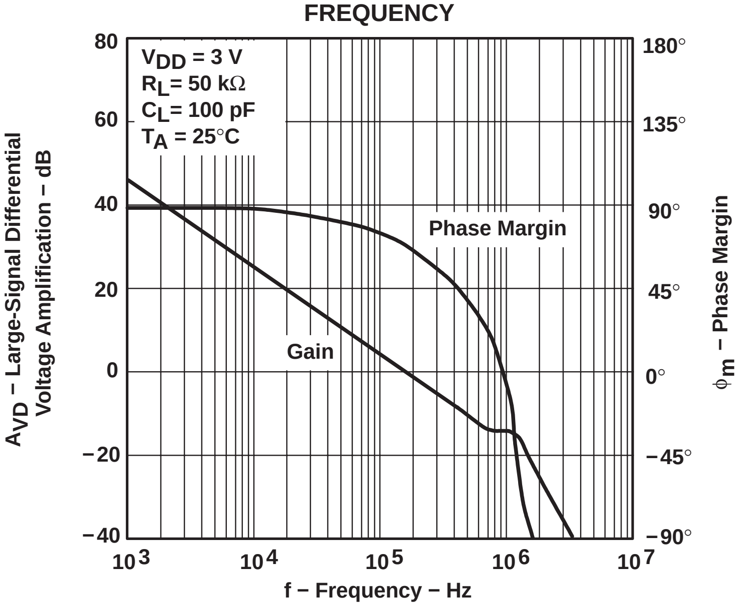


Figure 27

† For all curves where V_{DD} = 5 V, all loads are referenced to 2.5 V. For all curves where V_{DD} = 3 V, all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

LARGE-SIGNAL DIFFERENTIAL†‡ VOLTAGE AMPLIFICATION vs FREE-AIR TEMPERATURE

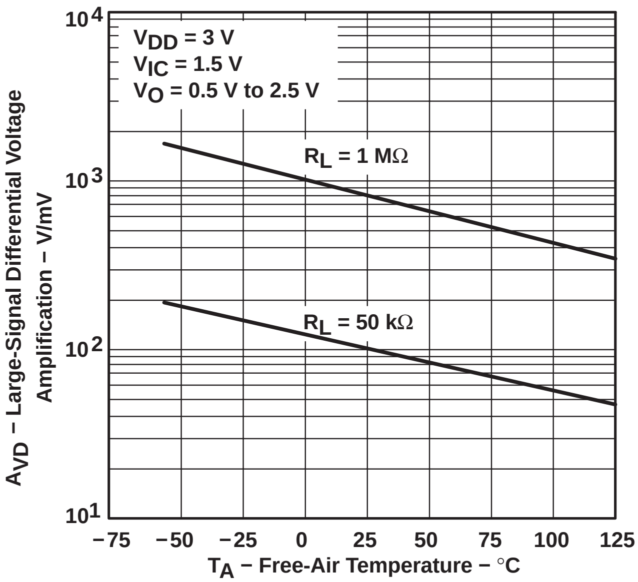


Figure 28

LARGE-SIGNAL DIFFERENTIAL†‡ VOLTAGE AMPLIFICATION vs FREE-AIR TEMPERATURE

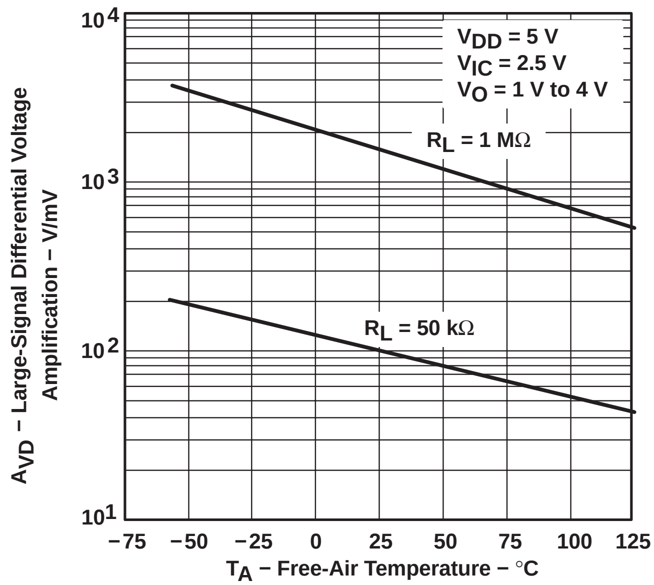


Figure 29

OUTPUT IMPEDANCE‡ vs FREQUENCY

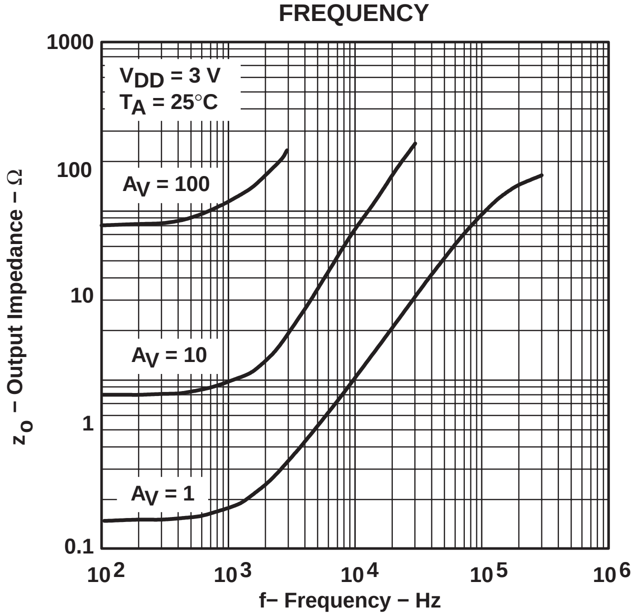


Figure 30

OUTPUT IMPEDANCE‡ vs FREQUENCY

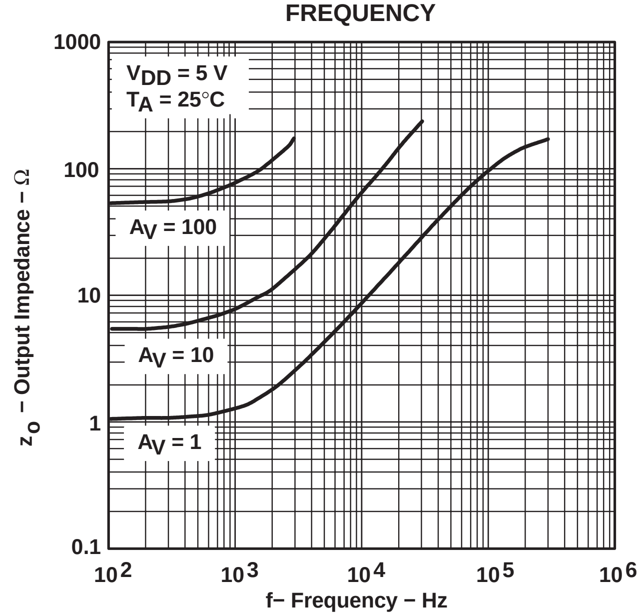


Figure 31

† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.
‡ For all curves where V_{DD} = 5 V, all loads are referenced to 2.5 V. For all curves where V_{DD} = 3 V, all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

COMMON-MODE REJECTION RATIO† vs FREQUENCY

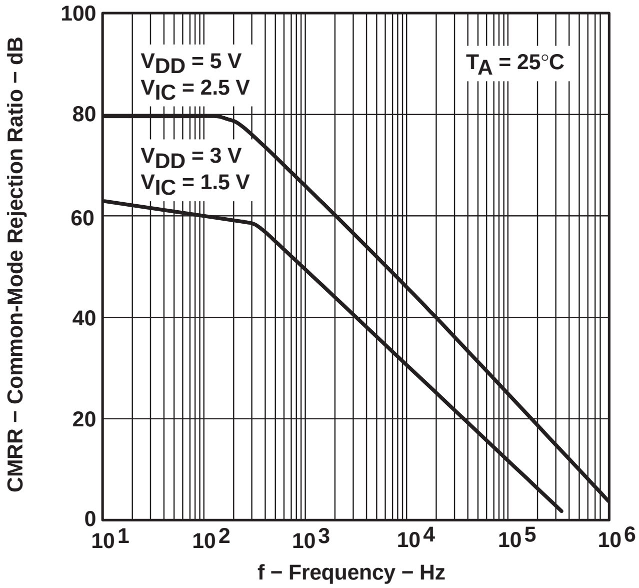


Figure 32

COMMON-MODE REJECTION RATIO†‡ vs FREE-AIR TEMPERATURE

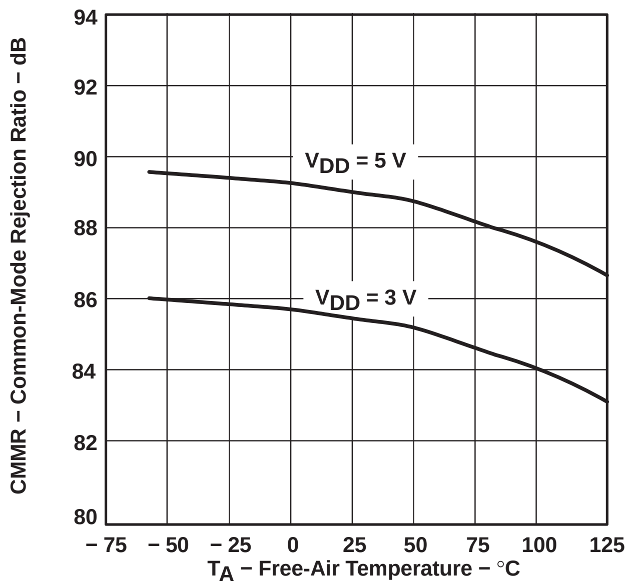


Figure 33

SUPPLY-VOLTAGE REJECTION RATIO† vs FREQUENCY

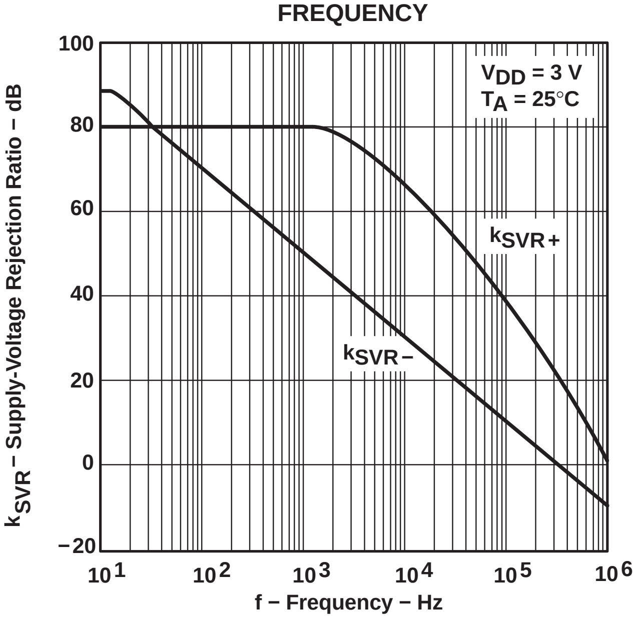


Figure 34

SUPPLY-VOLTAGE REJECTION RATIO† vs FREQUENCY

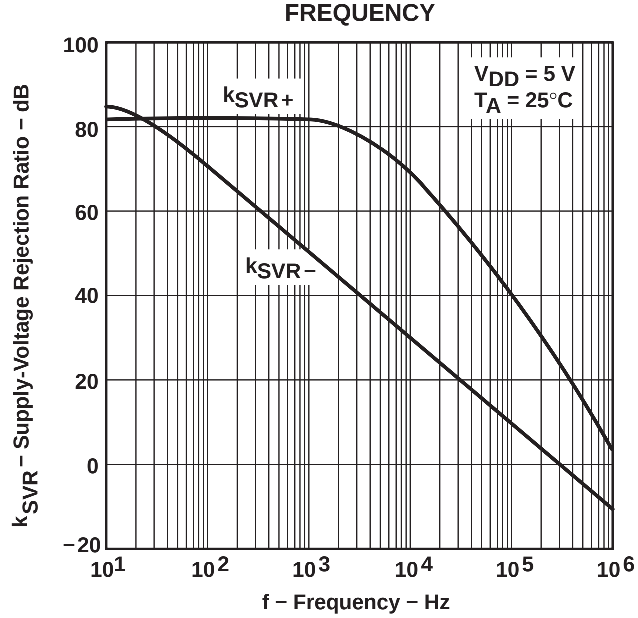


Figure 35

† For all curves where V_{DD} = 5 V, all loads are referenced to 2.5 V. For all curves where V_{DD} = 3 V, all loads are referenced to 1.5 V.
‡ Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

TYPICAL CHARACTERISTICS

SUPPLY-VOLTAGE REJECTION RATIO†
vs
FREE-AIR TEMPERATURE

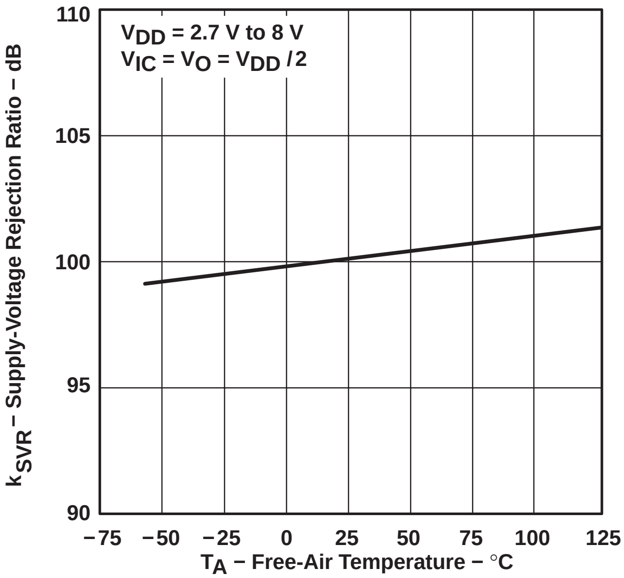


Figure 36

TLV2252
SUPPLY CURRENT†
vs
SUPPLY VOLTAGE

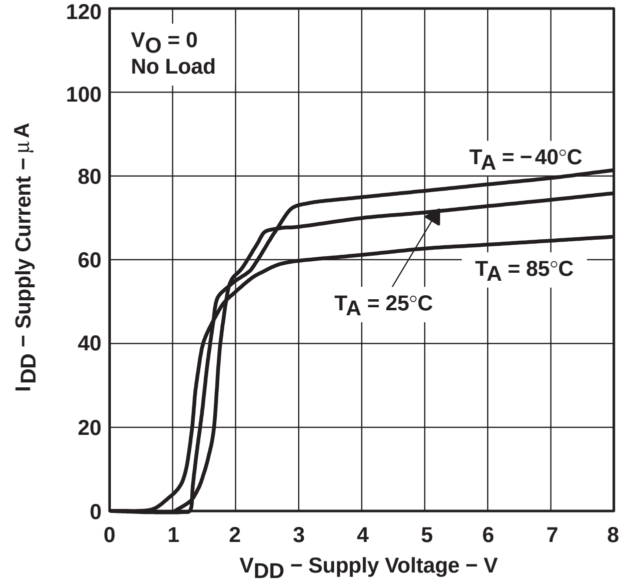


Figure 37

TLV2254
SUPPLY CURRENT†
vs
SUPPLY VOLTAGE

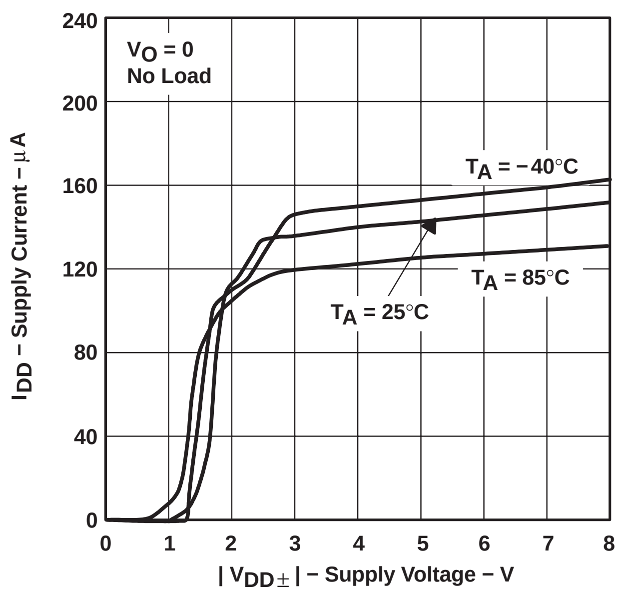


Figure 38

SLEW RATE‡
vs
LOAD CAPACITANCE

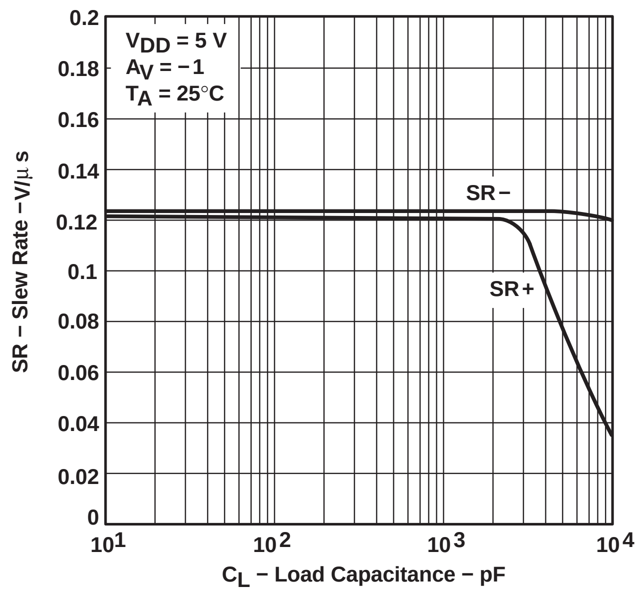


Figure 39

† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.
‡ For all curves where V_{DD} = 5 V, all loads are referenced to 2.5 V. For all curves where V_{DD} = 3 V, all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

SLEW RATE†‡ vs FREE-AIR TEMPERATURE

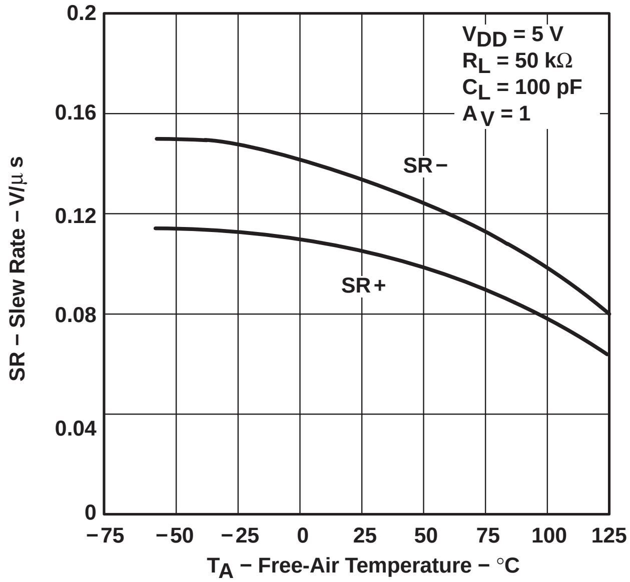


Figure 40

INVERTING LARGE-SIGNAL PULSE RESPONSE†

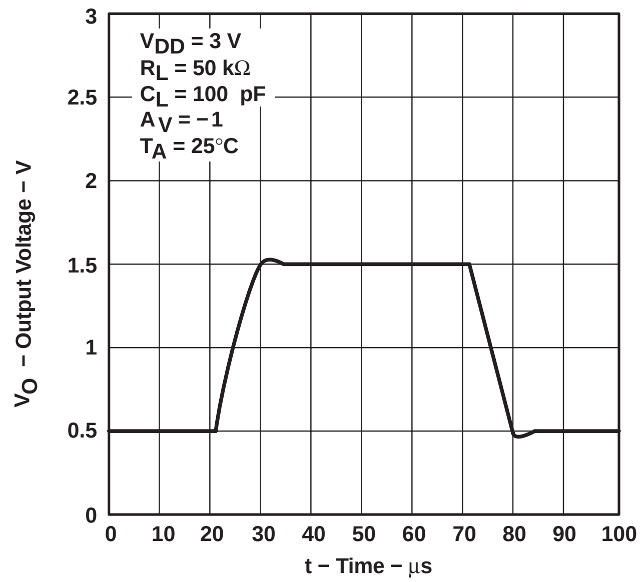


Figure 41

INVERTING LARGE-SIGNAL PULSE RESPONSE†

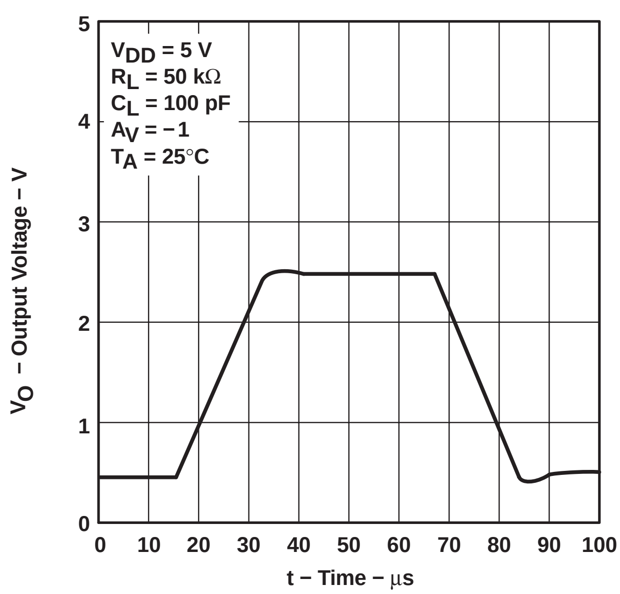


Figure 42

VOLTAGE-FOLLOWER LARGE-SIGNAL PULSE RESPONSE†

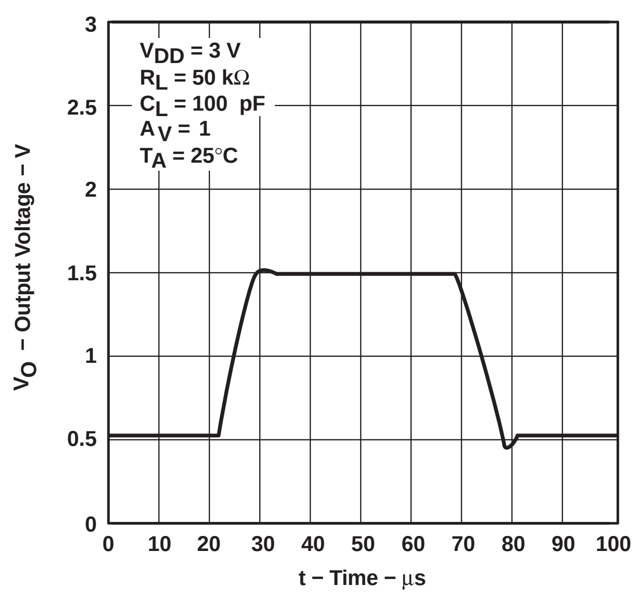


Figure 43

† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.
‡ For all curves where V_{DD} = 5 V, all loads are referenced to 2.5 V. For all curves where V_{DD} = 3 V, all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

VOLTAGE-FOLLOWER LARGE-SIGNAL PULSE RESPONSE†

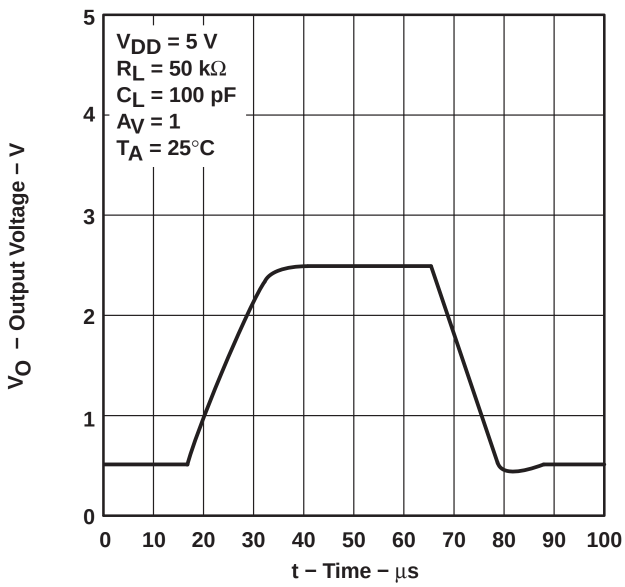


Figure 44

INVERTING SMALL-SIGNAL PULSE RESPONSE†

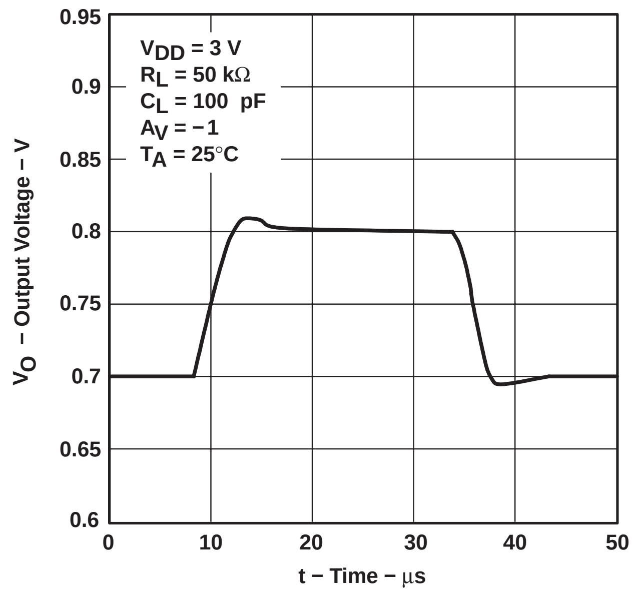


Figure 45

INVERTING SMALL-SIGNAL PULSE RESPONSE†

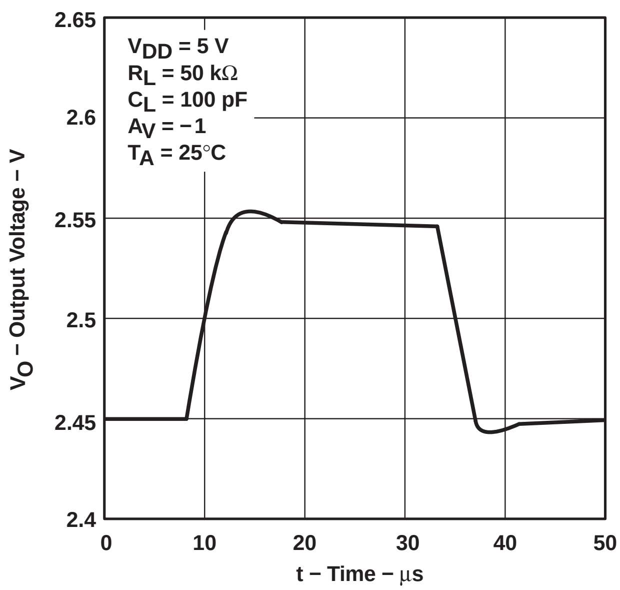


Figure 46

VOLTAGE-FOLLOWER SMALL-SIGNAL PULSE RESPONSE†

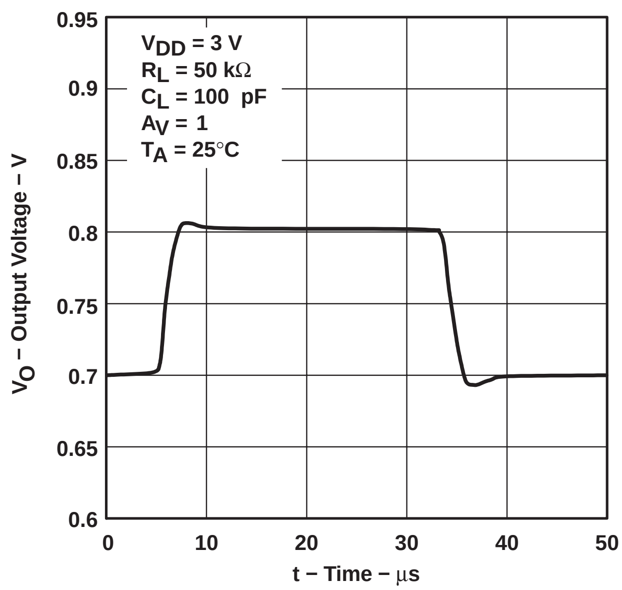


Figure 47

† For all curves where V_{DD} = 5 V, all loads are referenced to 2.5 V. For all curves where V_{DD} = 3 V, all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

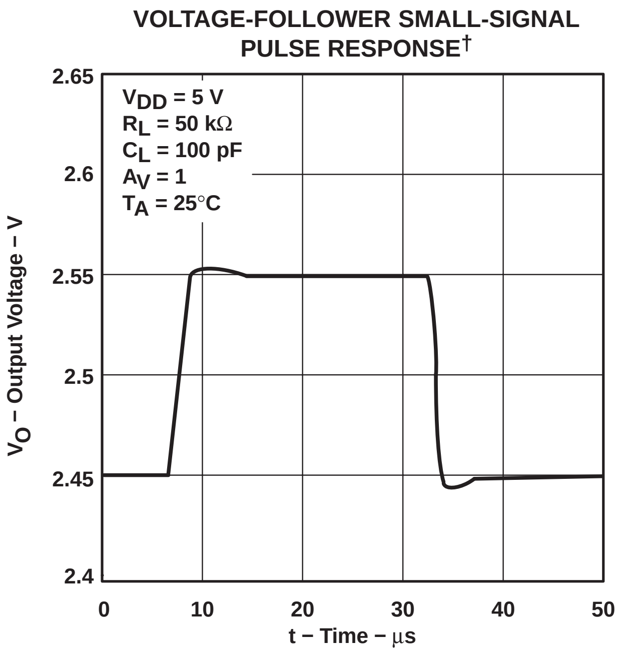


Figure 48

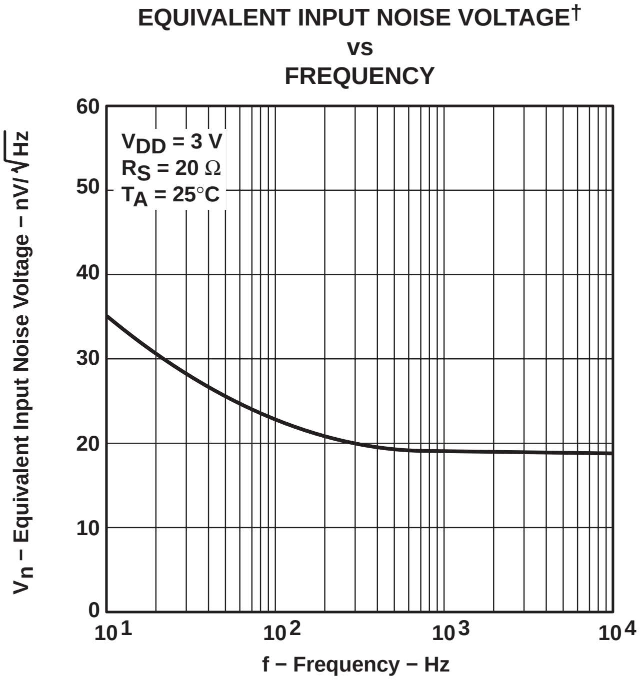


Figure 49

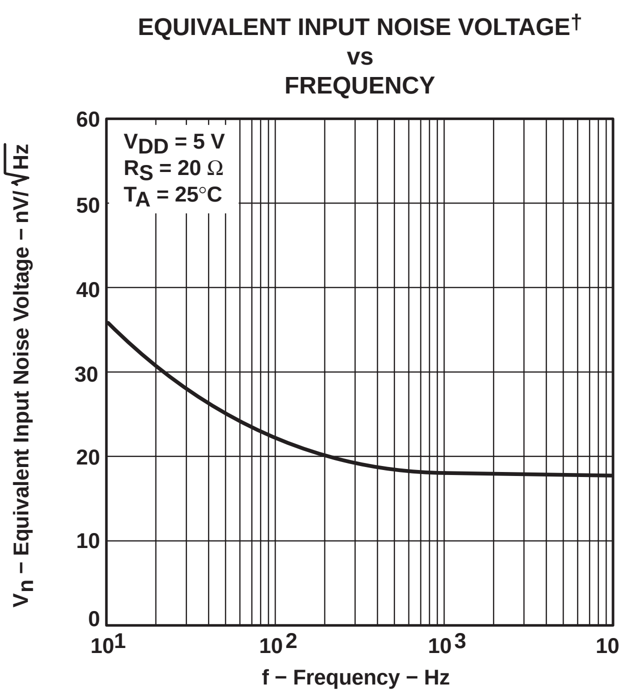


Figure 50

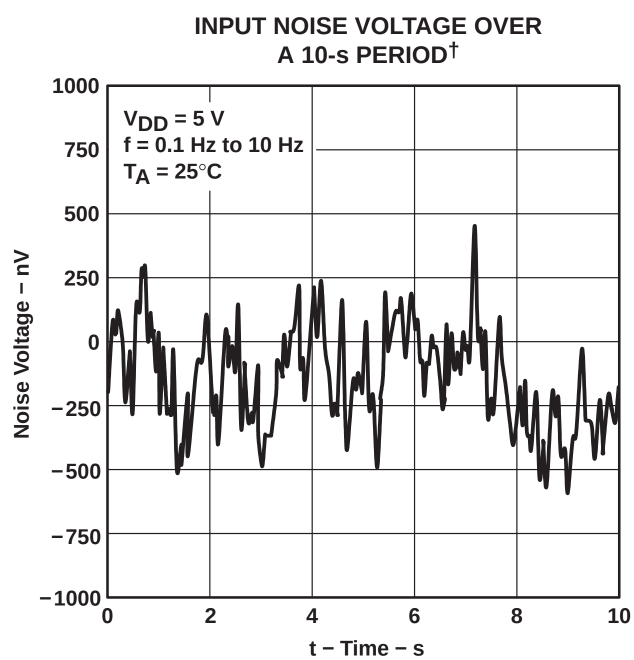


Figure 51

† For all curves where V_{DD} = 5 V, all loads are referenced to 2.5 V. For all curves where V_{DD} = 3 V, all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

INTEGRATED NOISE VOLTAGE† vs FREQUENCY

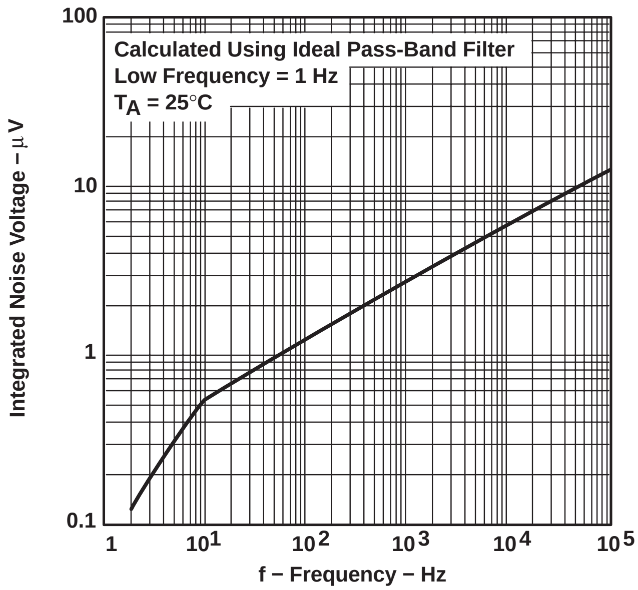


Figure 52

TOTAL HARMONIC DISTORTION PLUS NOISE† vs FREQUENCY

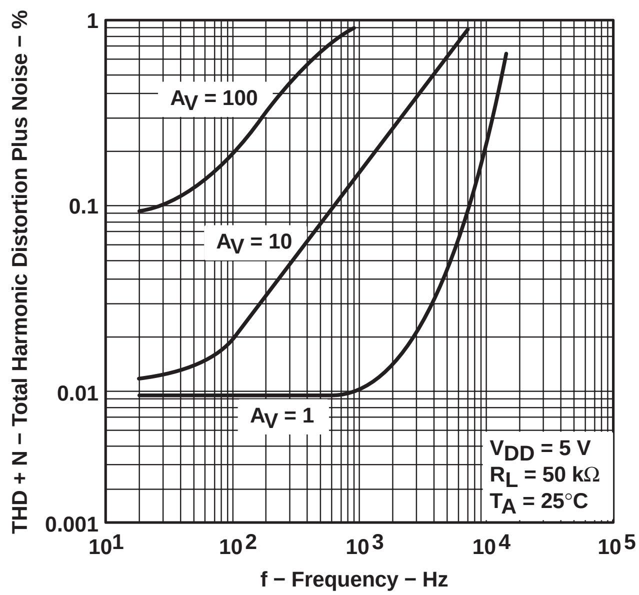


Figure 53

GAIN-BANDWIDTH PRODUCT vs SUPPLY VOLTAGE

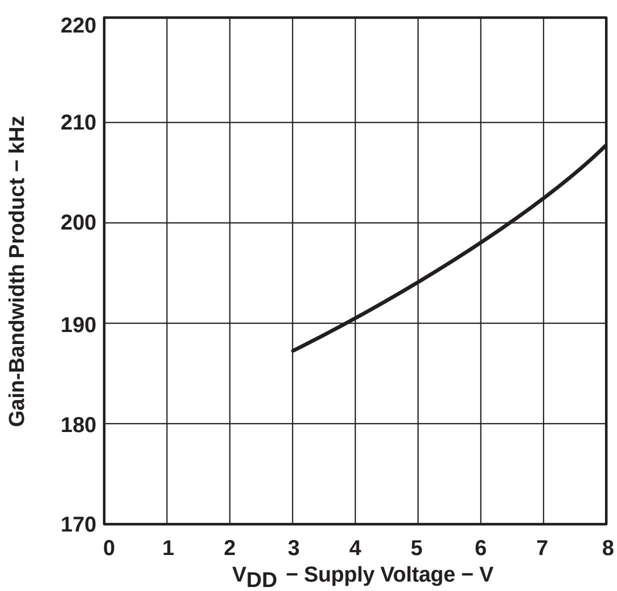


Figure 54

GAIN-BANDWIDTH PRODUCT†‡ vs FREE-AIR TEMPERATURE

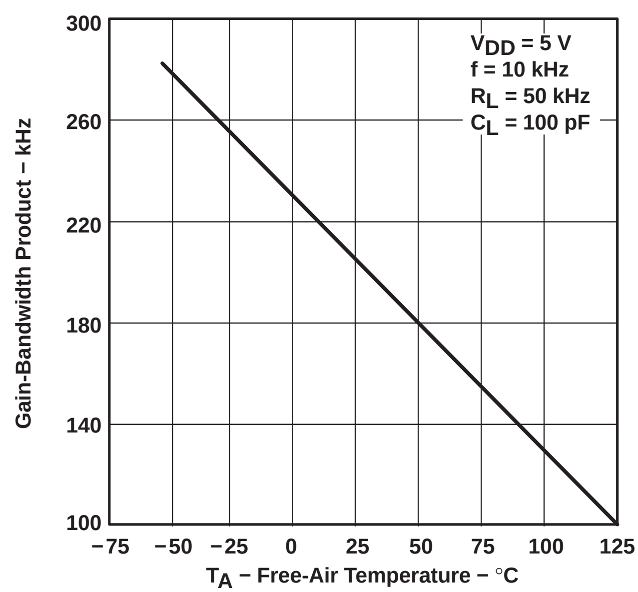


Figure 55

† For all curves where V_{DD} = 5 V, all loads are referenced to 2.5 V. For all curves where V_{DD} = 3 V, all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

PHASE MARGIN vs LOAD CAPACITANCE

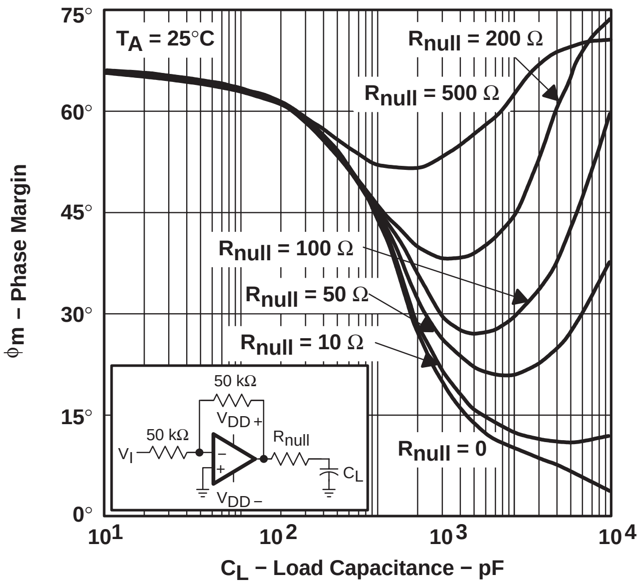


Figure 56

GAIN MARGIN vs LOAD CAPACITANCE

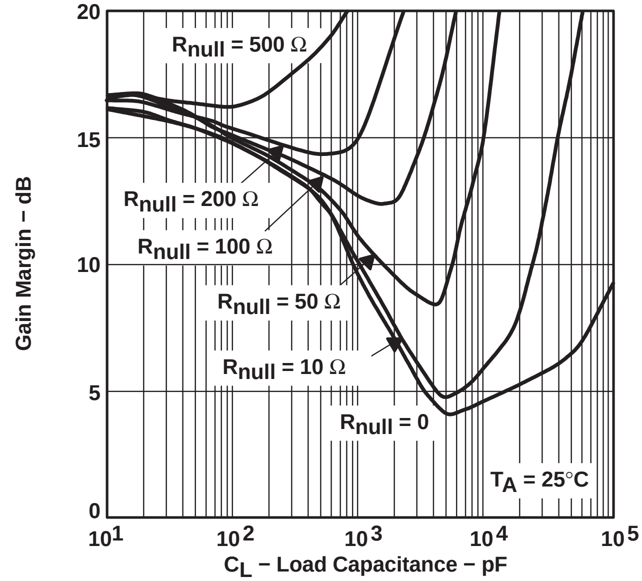


Figure 57

UNITY-GAIN BANDWIDTH vs LOAD CAPACITANCE

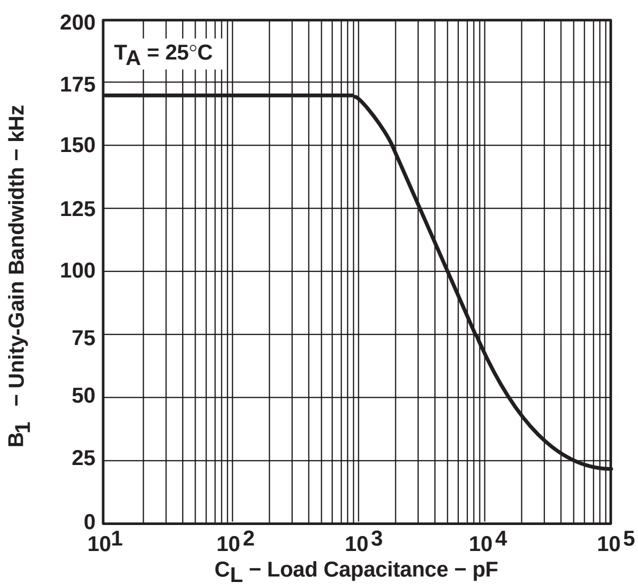
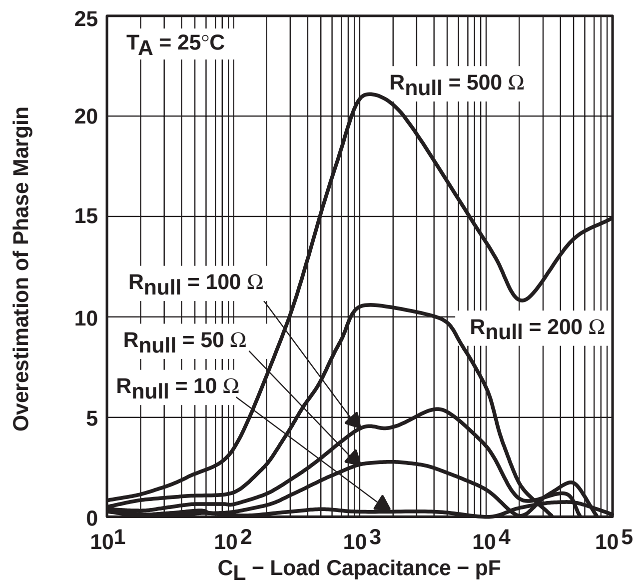


Figure 58

OVERESTIMATION OF PHASE MARGIN† vs LOAD CAPACITANCE



† See application information

Figure 59

† For all curves where V_{DD} = 5 V, all loads are referenced to 2.5 V. For all curves where V_{DD} = 3 V, all loads are referenced to 1.5 V.
‡ Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

APPLICATION INFORMATION

driving large capacitive loads

The TLV2252 is designed to drive larger capacitive loads than most CMOS operational amplifiers. Figure 56 and Figure 57 illustrate its ability to drive loads up to 1000 pF while maintaining good gain and phase margins (R_{null} = 0).

A smaller series resistor (R_{null}) at the output of the device (see Figure 60) improves the gain and phase margins when driving large capacitive loads. Figure 55 and Figure 56 show the effects of adding series resistances of 10 Ω, 50 Ω, 100 Ω, 200 Ω, and 500 Ω. The addition of this series resistor has two effects – the first adds a zero to the transfer function and the second reduces the frequency of the pole associated with the output load in the transfer function.

The zero introduced to the transfer function is equal to the series resistance times the load capacitance. To calculate the improvement in phase margin, equation 1 can be used.

$$\Delta\phi_{m1} = \tan^{-1}\left(2 \times \pi \times UGBW \times R_{null} \times C_L\right) \qquad (1)$$

Where :

$\Delta\phi_{m1}$ = improvement in phase margin
UGBW = unity-gain bandwidth frequency
R_{null} = output series resistance
C_L = load capacitance

The unity-gain bandwidth (UGBW) frequency decreases as the capacitive load increases (see Figure 58). To use equation 1, UGBW must be approximated from Figure 58.

Using equation 1 alone overestimates the improvement in phase margin as illustrated in Figure 59. The overestimation is caused by the decrease in the frequency of the pole associated with the load, providing additional phase shift and reducing the overall improvement in phase margin.

Using Figure 60, with equation 1 enables the designer to choose the appropriate output series resistance to optimize the design of circuits driving large capacitance loads.

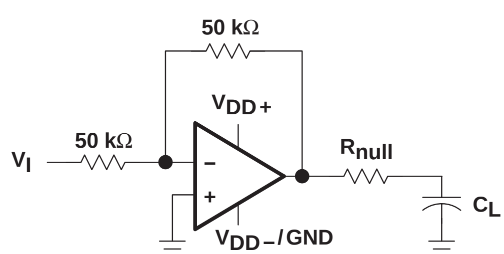


Figure 60. Series-Resistance Circuit

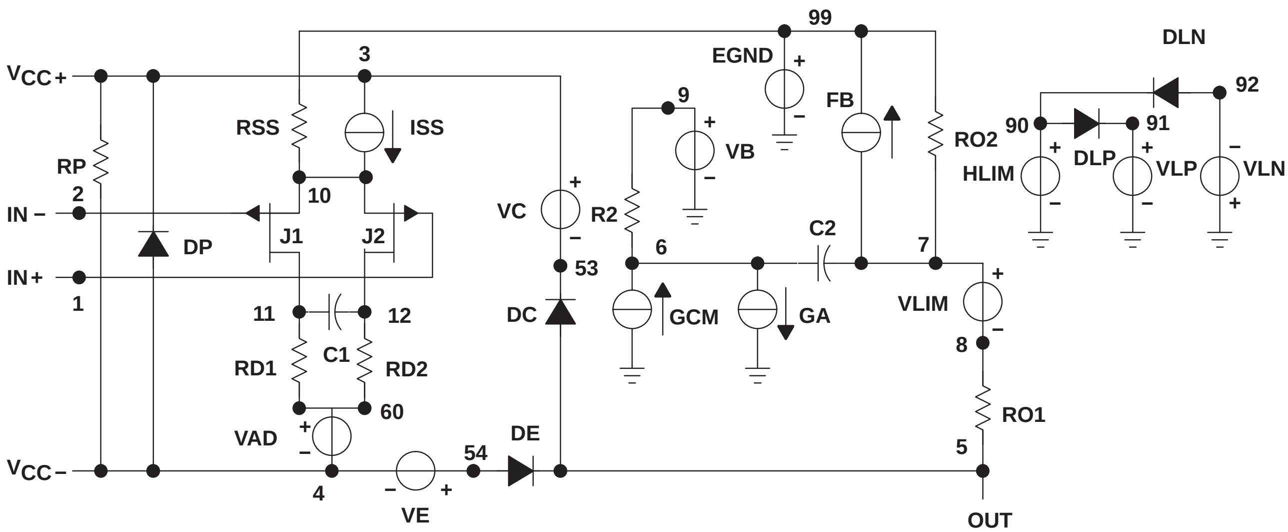
APPLICATION INFORMATION

macromodel information

Macromodel information provided was derived using Microsim *Parts*™, the model generation software used with Microsim *PSpice*™. The Boyle macromodel (see Note 5) and subcircuit in Figure 61 are generated using the TLV2252 typical electrical and operating characteristics at T_A = 25°C. Using this information, output simulations of the following key parameters can be generated to a tolerance of 20% (in most cases):

- Maximum positive output voltage swing
- Maximum negative output voltage swing
- Slew rate
- Quiescent power dissipation
- Input bias current
- Open-loop voltage amplification
- Unity-gain frequency
- Common-mode rejection ratio
- Phase margin
- DC output resistance
- AC output resistance
- Short-circuit output current limit

NOTE 4: G. R. Boyle, B. M. Cohn, D. O. Pederson, and J. E. Solomon, “Macromodeling of Integrated Circuit Operational Amplifiers,” *IEEE Journal of Solid-State Circuits,* SC-9, 353 (1974).




```
.SUBCKT TLV225x 1 2 3 4 5
C1     11   12   6.369E−12
C2     6    7    25.00E−12
DC     5    53   DX
DE     54   5    DX
DLP    90   91   DX
DLN    92   90   DX
DP     4    3    DX
EGND   99   0    POLY (2) (3,0) (4,0) 0 .5 .5
FB     7    99   POLY (5) VB VC VE VLP
+ VLN 0 57.62E6 −60E6 60E6 60E6 −60E6
GA     6    0    11   12 26.86E−6
GCM    0    6    10   99 2.686E−9
ISS    3    10   DC 3.1E−6
HLIM   90   0    VLIM 1K
J1     11   2    10 JX
J2     12   1    10 JX
R2     6    9    100.0E3

RD1    60   11   37.23E3
RD2    60   12   37.23E3
R01    8    5    84
R02    7    99   84
RP     3    4    71.43E3
RSS    10   99   64.52E6
VAD    60   4    −.5
VB     9    0    DC 0
VC     3    53   DC .605
VE     54   4    DC .605
VLIM   7    8    DC 0
VLP    91   0    DC −0.235
VLN    0    92   DC 7.5
.MODEL DX D (IS=800.0E−18)
.MODEL JX PJF (IS=500.0E−15 BETA=139E−6
+ VTO=−.05)
.ENDS
```

Figure 61. Boyle Macromodel and Subcircuit

PSpice and *Parts* are trademarks of MicroSim Corporation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish	MSL Peak Temp (3)
TLV2252AQDREP	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLV2252QDREP	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLV2254AQDREP	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLV2254QDREP	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
V62/04651-01UE	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
V62/04651-02UE	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
V62/04651-03XE	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
V62/04651-04XE	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.
TBD: The Pb-Free/Green conversion plan has not been defined.
Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.
Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.
Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF TLV2252-EP, TLV2252A-EP, TLV2254-EP, TLV2254A-EP :

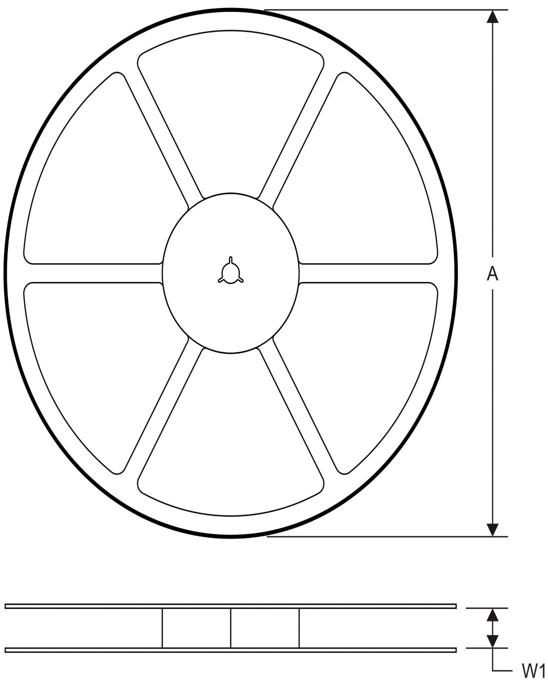
- Catalog: TLV2252, TLV2252A, TLV2254, TLV2254A
- Automotive: TLV2252-Q1, TLV2252A-Q1, TLV2254-Q1, TLV2254A-Q1
- Military: TLV2252M, TLV2252AM, TLV2254M, TLV2254AM

NOTE: Qualified Version Definitions:

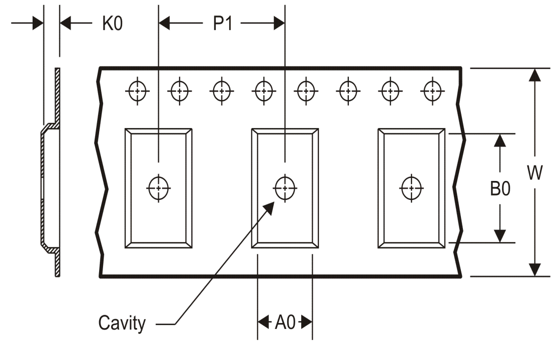
- Catalog - TI's standard catalog product
- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects
- Military - QML certified for Military and Defense Applications

TAPE AND REEL INFORMATION

REEL DIMENSIONS



TAPE DIMENSIONS



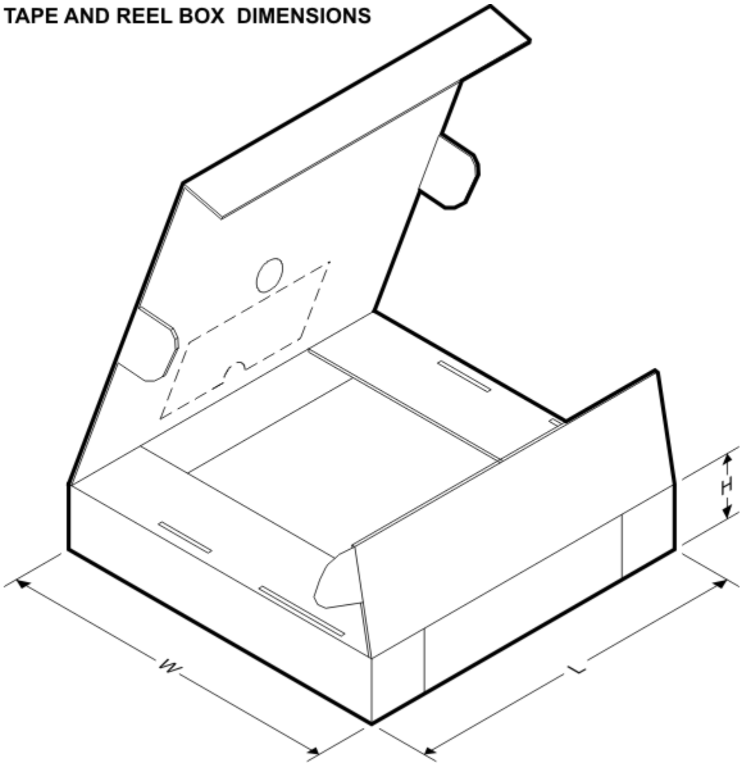
A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

TAPE AND REEL INFORMATION

*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLV2252AQDREP	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TLV2252QDREP	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TLV2254AQDREP	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TLV2254QDREP	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1

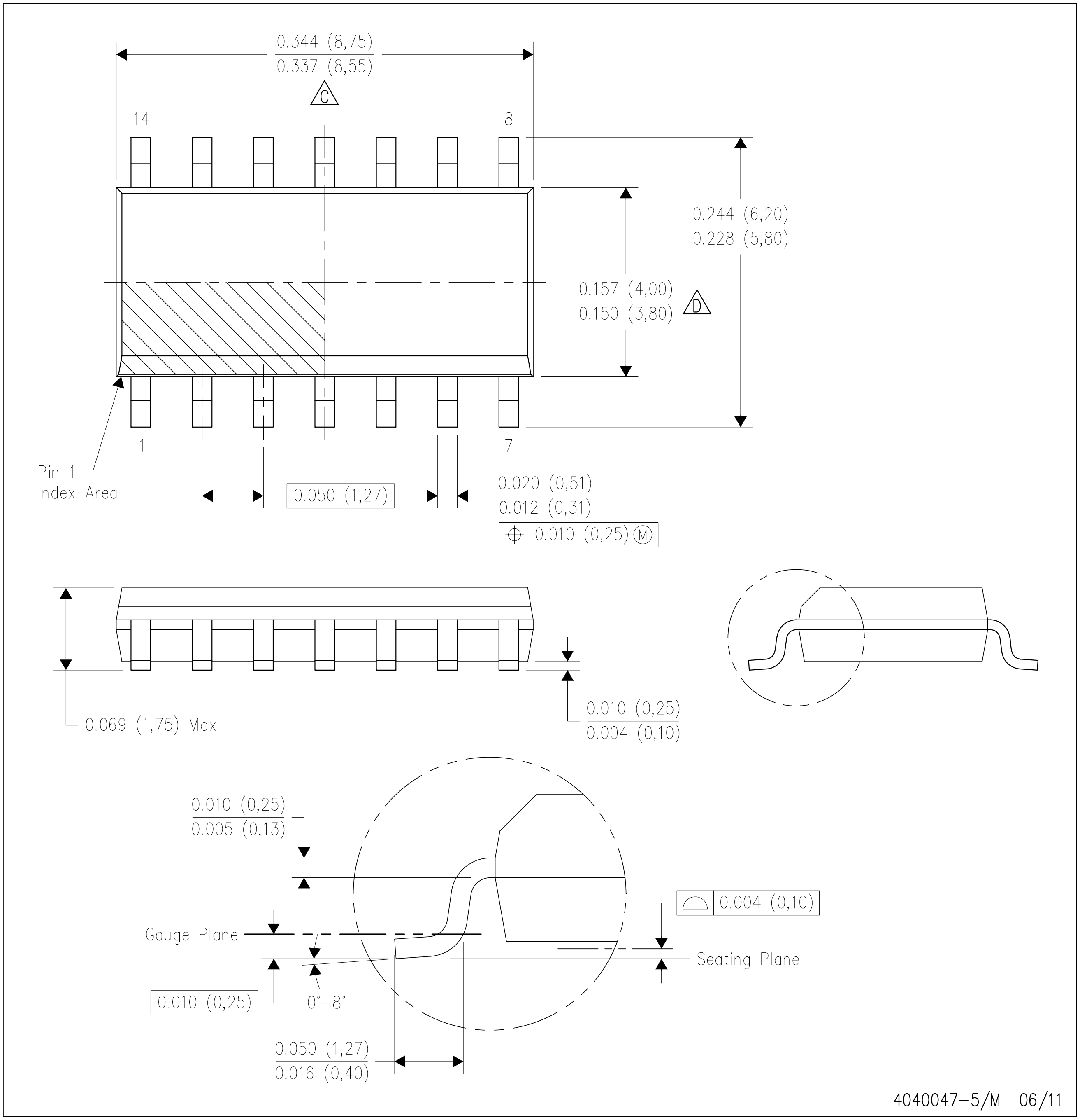
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

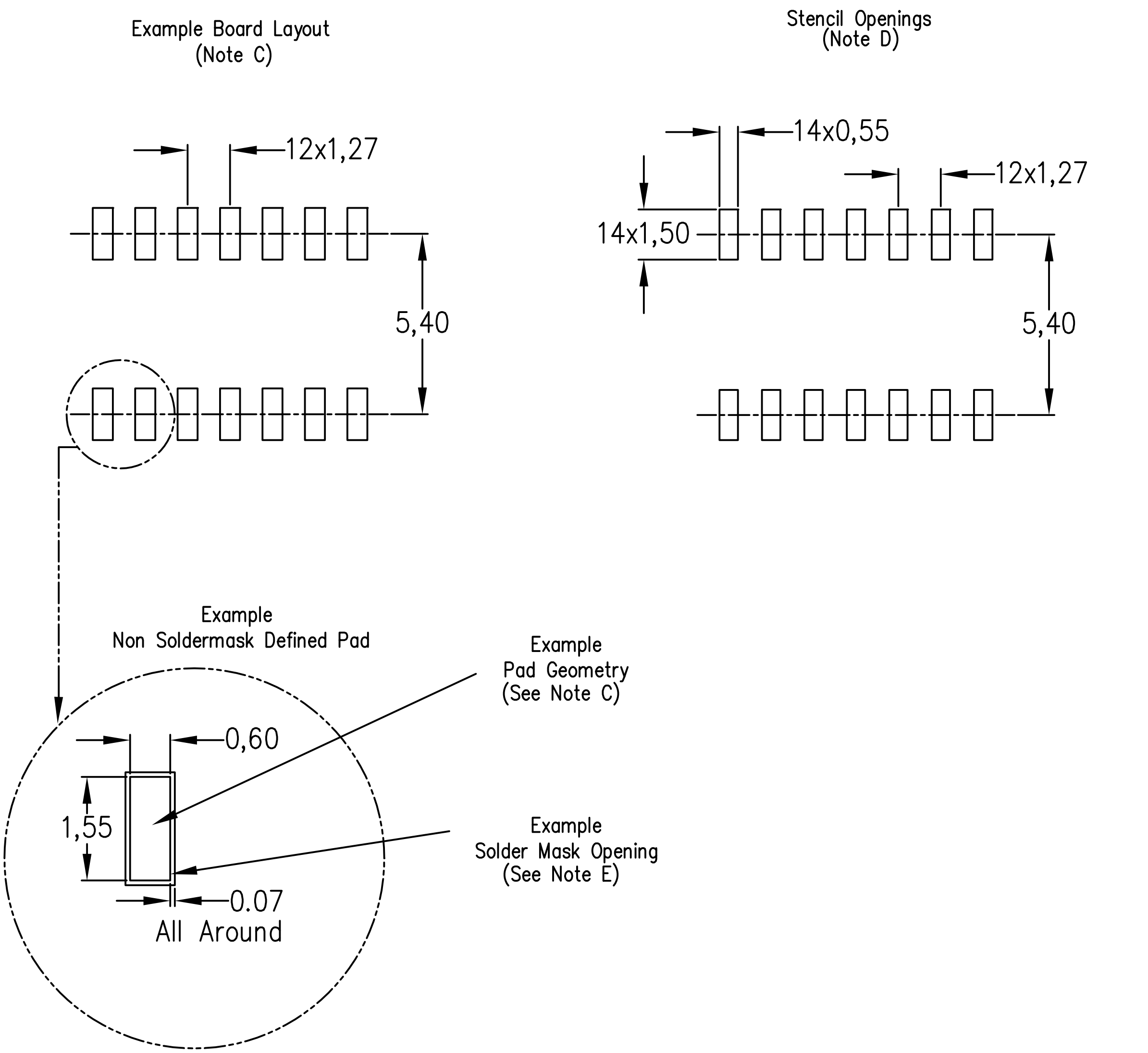
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLV2252AQDREP	SOIC	D	8	2500	367.0	367.0	35.0
TLV2252QDREP	SOIC	D	8	2500	367.0	367.0	35.0
TLV2254AQDREP	SOIC	D	14	2500	333.2	345.9	28.6
TLV2254QDREP	SOIC	D	14	2500	333.2	345.9	28.6

D (R–PDSO–G14) PLASTIC SMALL OUTLINE



NOTES:
- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- D. Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AB.

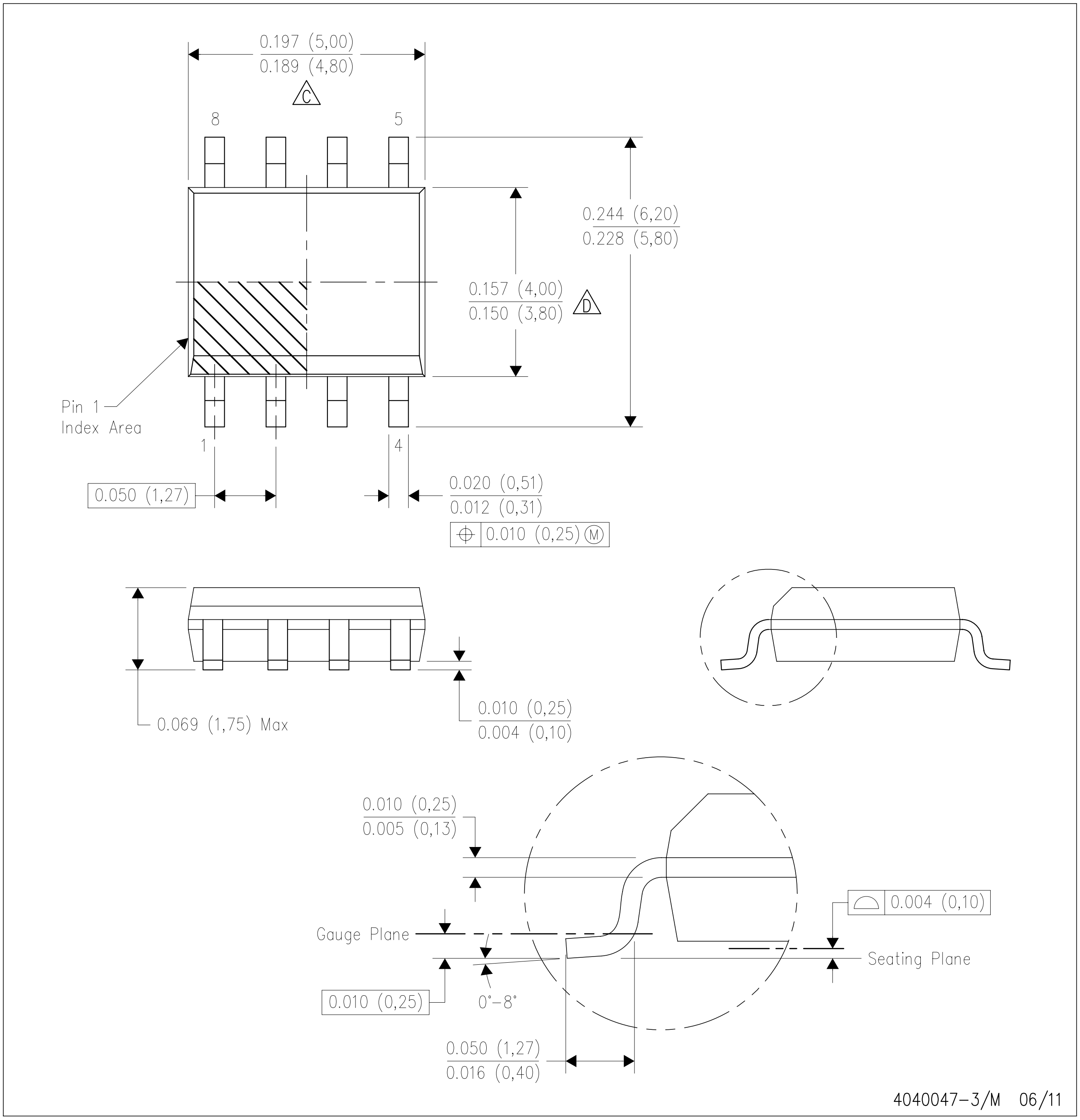
D (R-PDSO-G14) PLASTIC SMALL OUTLINE



4211283-3/E 08/12

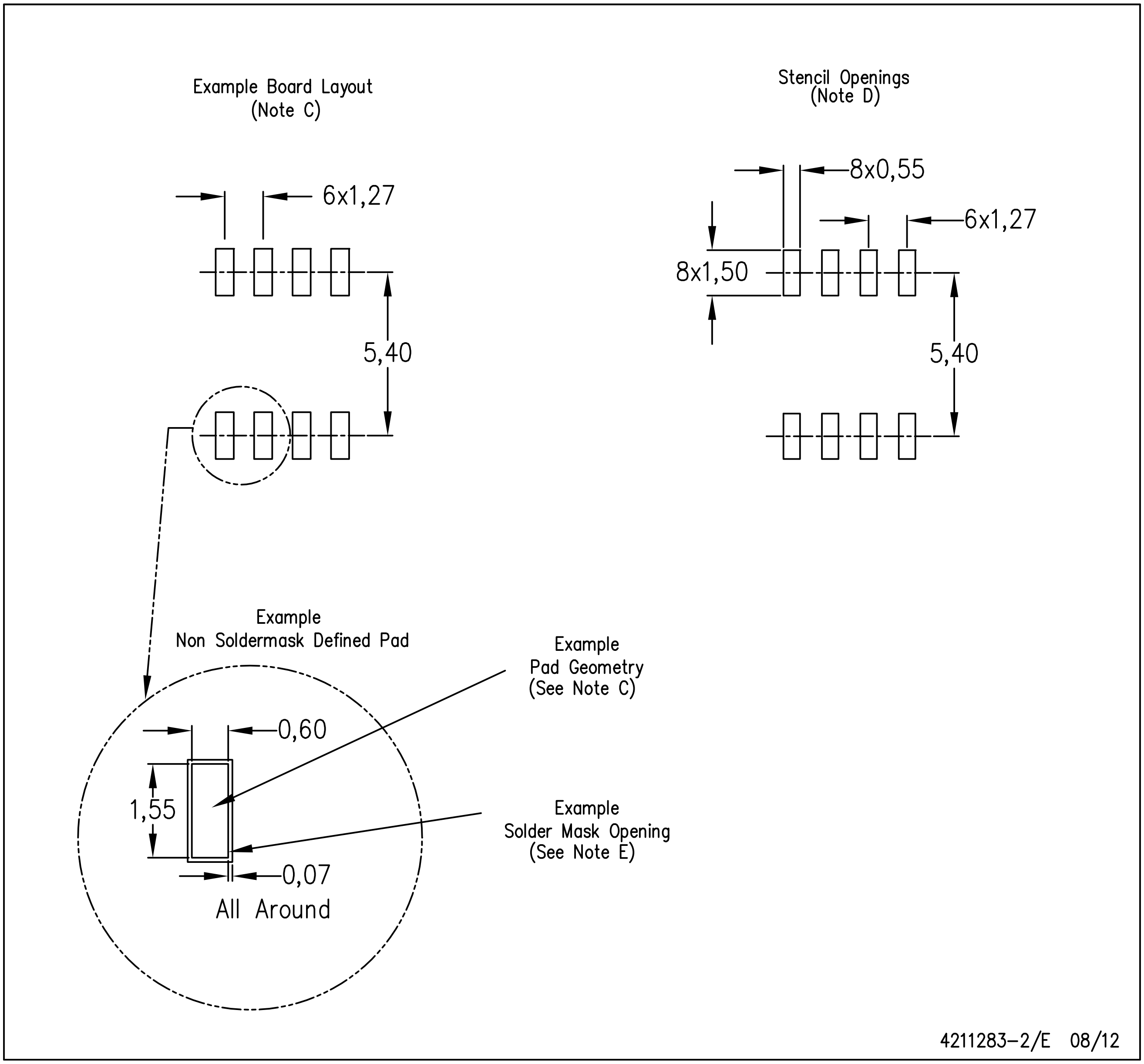
NOTES:
- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

D (R-PDSO-G8) PLASTIC SMALL OUTLINE



NOTES:
- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- D. Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AA.

D (R-PDSO-G8) PLASTIC SMALL OUTLINE



NOTES:
- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

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